



## RF and Wireless Systems

### Data Sheet

# MT6162 (Othello H)

|                      |               |
|----------------------|---------------|
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# Multi-band Multi-mode Single Chip HEDGE Transceiver

Preliminary Datasheet

MT6162

Konka WCX

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Konka WCX

**INTRODUCTION**

The MT6162 is a single-chip multi-mode multi-band transceiver offering unparalleled integration and feature set resulting in industry's lowest eBoM. It is fully compliant with 3G mode (3GPP Rel. 6), as well as supporting GSM/GPRS/EDGE modes (GGE). It constitutes with MediaTek's baseband modem ICs a complete chipset solution for 3G and GGE cellular user equipment. Quad-band GGE and a wide range of 3G bands support (I - VI, VIII - X) is provided in terms of both frequency ranges and the flexibility of band allocation.

The direct conversion receiver is part of an over-sampled sigma-delta architecture, which shifts more signal conditioning to digital baseband (DBB) and results in optimum HSDPA throughput. The direct modulation transmitter (8PSK/3G), combined with a low noise GMSK constant envelope modulator or DFM (Direct-Frequency Modulation), delivers high modulation accuracy with exceptionally low noise and eliminates the need for transmit SAW filters in any of the supported GGE and 3G modes. On-chip impairments compensation is used to guarantee optimum 3G Rx and Tx performance. The 3G receiver operation is SAW-less and does not require any Rx SAW filters post LNAs. Two on-chip VCOs at 2xLO/4xLO frequencies provide the two local oscillators required for RX and TX sections; they are followed by frequency dividers and are locked to the system reference via two fast-settling RF Fractional-N PLLs.

All functional and PLL programming is done via a 3-wire serial bus. The chip operates from 2.8V and 1.8V regulated supplies from a PMT sub-system in the baseband section, and is housed in a 6.2x6.2mm<sup>2</sup> 62-pin aQFN package with an offset array 0.666mm pin spacing (minimum pin to pin distance 0.47mm).

**FEATURES****General**

Fully integrated single chip RF Transceiver

Quad-band GSM/EDGE operation

Multi-band (I – VI, and VIII – X) 3G FDD operation

Part of MTK's turnkey platform solutions with best-in-class performance and industry's lowest eBoM due to smart architecture choice

Compliant with 3GPP HSDPA/HSUPA Release 6

On-chip correction for RF impairments, with digital baseband support for optimum TRx performance and reduced chip calibration test time

Lead free 62-pin aQFN package (6.2x6.2mm<sup>2</sup>)

**Transmitter**

Low noise GMSK/ 8PSK/ 3G TX modulator eliminating external SAW filters, with Direct-Frequency Modulation TX for GSM mode

Dedicated Tx drivers that can support radio configuration with multi-mode multi-Band PAs

Excellent 3G EVM performance over the full Tx dynamic range

High dynamic range integrated synchronous power detector, with ultra-fast TX power control support

Low Tx supply current from Vbat: Typical 48mA (3G avg. DG09, Band I); 36mA (GMSK DFM)

**Receiver**

High performance SAW-less (3G only) direct conversion receiver, with differential input LNAs

Receiver with superior sensitivity and blocking margins

Low Rx supply current from Vbat: Typical 37mA (3G avg. DG09, Band I); 40mA (GSM/EDGE)

**Frequency Synthesizers**

Fast settling synthesizers, with 26MHz internal DCXO or external VCTCXO reference

### APPLICATIONS

Single and multi band / mode 3G handsets  
 3G/HSDPA/HSUPA Wireless data modems (3GPP Release 6)  
 WEDGE / HEDGE solutions

### FUNCTIONAL BLOCK DIAGRAM

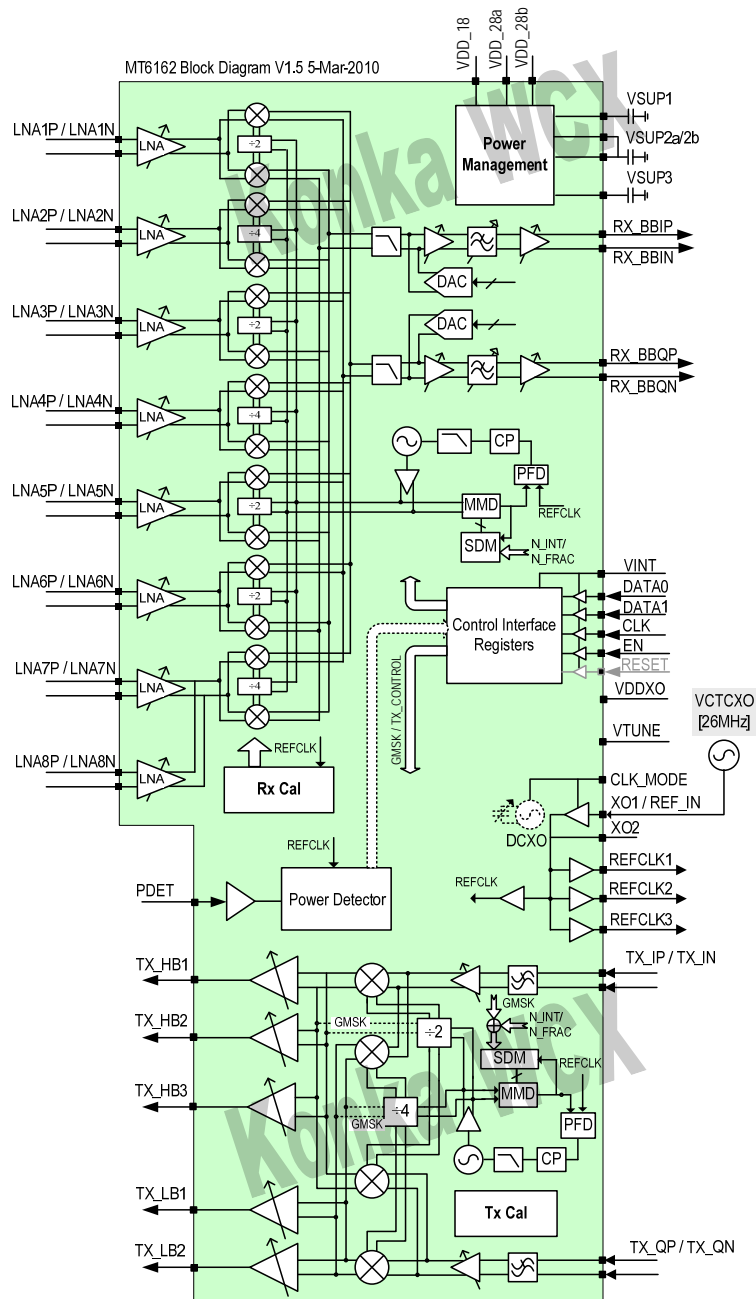


Figure 1

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## OPERATING CONDITIONS

Table 1

| Parameter                                     | Symbol             | Min   | Typ   | Max   | Unit   | Comments   |
|---|--------------------|-------|-------|-------|--------|--|
| Reference Supply                              | V <sub>DD_28</sub> | 2.75  | 2.85  | 2.95  | V      | Linear regulated supply  |
|   | V <sub>DD_18</sub> | 1.75  | 1.825 | 1.9   | V      | Switching regulated supply   |
|   | V <sub>INT</sub>   | 1.675 | 1.8   | 1.925 | V      | Serial interface control logic   |
| VCXO/DCXO Supply                              | V <sub>DDXO</sub>  | 2.7   | 2.8   | 2.9   | V      | Linear regulated supply  |
| Ambient Temperature                           | T <sub>amb</sub>   | -30   | 25    | 85    | °C     |  |
| Rx baseband load capacitance                  | C <sub>LD</sub>    |       |       | 10    | pF     | Equivalent Differential <sup>1)</sup>  |
| Rx baseband load resistance                   | R <sub>Ld</sub>    | 20    | 32    | 45    | kΩ     | Differential   |
| Rx required amplitude balance                 | DA <sub>diff</sub> | -1    |       | 1     | dB     | All Rx input pairs   |
| Rx required phase balance                     | Df <sub>diff</sub> | -10   |       | 10    | deg    | All Rx input pairs   |
| Tx baseband I/Q common mode                   | V <sub>CM</sub>    | 1.05  | 1.1   | 1.15  | V      | Acceptable range with slight degradation <sup>2)</sup>   |
|   |                    | 1.05  |       | 1.25  | V      |  |
| Tx baseband I/Q differential Full-Scale input |                    | 940   | 990   | 1040  | mVppd  | 2.4dB allocated for Tx RF impairments compensation; 750mVppd effectively used for I/Q Tx BB signal |
| Tx baseband I/Q Input Resistance              |                    | 200   |       |       | kΩ     | Differential   |
| Tx baseband I/Q Input Capacitance             |                    |       |       | 2.5   | pF     | Differential<br>Single-Ended   |
|   |                    |       |       | 4.0   | pF     |  |
| High Band (HB) Transmitter Frequency          | F <sub>Tx</sub>    | 1920  |       | 1980  | MHz    | 3G Band I  |
|   |                    | 1850  |       | 1910  |        | 3G Band II / GSM1900   |
|   |                    | 1710  |       | 1785  |        | 3G Band III/IV/IX/X / GSM1800  |
| Low Band (LB) Transmitter Frequency           |                    | 824   |       | 849   | MHz    | 3G Band V/VI / GSM850  |
|   |                    | 880   |       | 915   |        | 3G Band VIII / GSM900  |
| High Band (HB) Receiver Frequency             | F <sub>Rx</sub>    | 2110  |       | 2170  | MHz    | 3G Band I/IV/X   |
|   |                    | 1930  |       | 1990  |        | 3G Band II / GSM1900   |
|   |                    | 1805  |       | 1880  |        | 3G Band III/IX / GSM1800   |
| Low Band (LB) Receiver Frequency              |                    | 869   |       | 894   | MHz    | 3G Band V/VI / GSM850  |
|   |                    | 925   |       | 960   |        | 3G Band VIII / GSM900  |
| Reference Input Clock (VCTCXO) Frequency      | F <sub>ref</sub>   |       | 26    |       | MHz    |  |
| Voltage Swing                                 |                    | 700   |       | 1500  | mVpp   |  |
| Duty Cycle                                    |                    | 40    |       | 60    | %      |  |
| Reference Input Clock (VCTCXO) Phase Noise    |                    |       |       | -106  | dBc/Hz | @ F <sub>offset</sub> = 100Hz  |
|   |                    |       |       | -134  | dBc/Hz | @ F <sub>offset</sub> = 1KHz   |
|   |                    |       |       | -144  | dBc/Hz | @ F <sub>offset</sub> = 10KHz  |
|   |                    |       |       | -148  | dBc/Hz | @ F <sub>offset</sub> = 100KHz   |
| Harmonic Content                              |                    |       |       | -8    | dBc    | HD2 @ 52MHz  |
|   |                    |       |       | -10   | dBc    | HD3 @ 78MHz  |
|   |                    |       |       | -20   | dBc    | HD4 @ 104MHz   |

<sup>1)</sup> V<sub>CM</sub> up to 1.25V causes no performance degradation for nominal silicon over ETC. For worst-case silicon, a ~1dB degradation in full chain ACLR can be expected.

<sup>2)</sup> The load capacitance can be either common mode (to AC ground) or differential. The specification is written in terms of an equivalent differential load capacitance. In reality, the split can be arbitrary between common mode and differential mode, and both scenarios must be considered. The maximum difference between C<sub>RX-GND</sub> and C<sub>RXB-GND</sub> is 1pF.

## ABSOLUTE MAXIMUM RATINGS

Table 2

| Parameter                      | Rating                             |
|--------------------------------|------------------------------------|
| VSUP3, VDD_28a/b, VDDXO        | -0.3 V to 3.6 V                    |
| VSUP1, VSUP2, VDD_18           | -0.3 V to 2.0 V                    |
| Serial Interface supply VINT   | -0.3 V to 2.0 V                    |
| Digital Input Voltage          | -0.3 to VINT+0.3V                  |
| Analog Input Voltage           | -0.3 to VDD28+0.3V                 |
| Storage Temperature            | -55 °C to 150 °C                   |
| Operating Junction Temperature | +125 °C                            |
| LNA Input Level                | +3dBm RF differential input (100Ω) |
| Power Detector Input Level     | +7dBm RF input (50Ω)               |
| Maximum power dissipation      | 750mW                              |

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### Notes

1. No DC input should be directly applied to the Rx inputs. Matching network should either be a series capacitor/inductor or shunt inductor (RXn/RXnB)
2. Tx Output is DC shorted to ground internally no DC should be applied under any circumstances (AC coupling required for those PA's with DC at the input)
3. VSUP1-VSUP3: No short circuit protect is implemented; no DC should be applied under any circumstances

## THERMAL RESISTANCE

Thermal resistance data is with a JEDEC standard PCB board.

Table 3 Thermal Resistance

| Package Type | $\Theta_{ja}$ (to ambient) | $\Psi_{jb}$ (to board) | Unit |
|--------------|----------------------------|------------------------|------|
| aQFN         | 26                         | 5                      | °C/W |

## ESD CAUTION



### ESD (electrostatic discharge) sensitive device.

Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

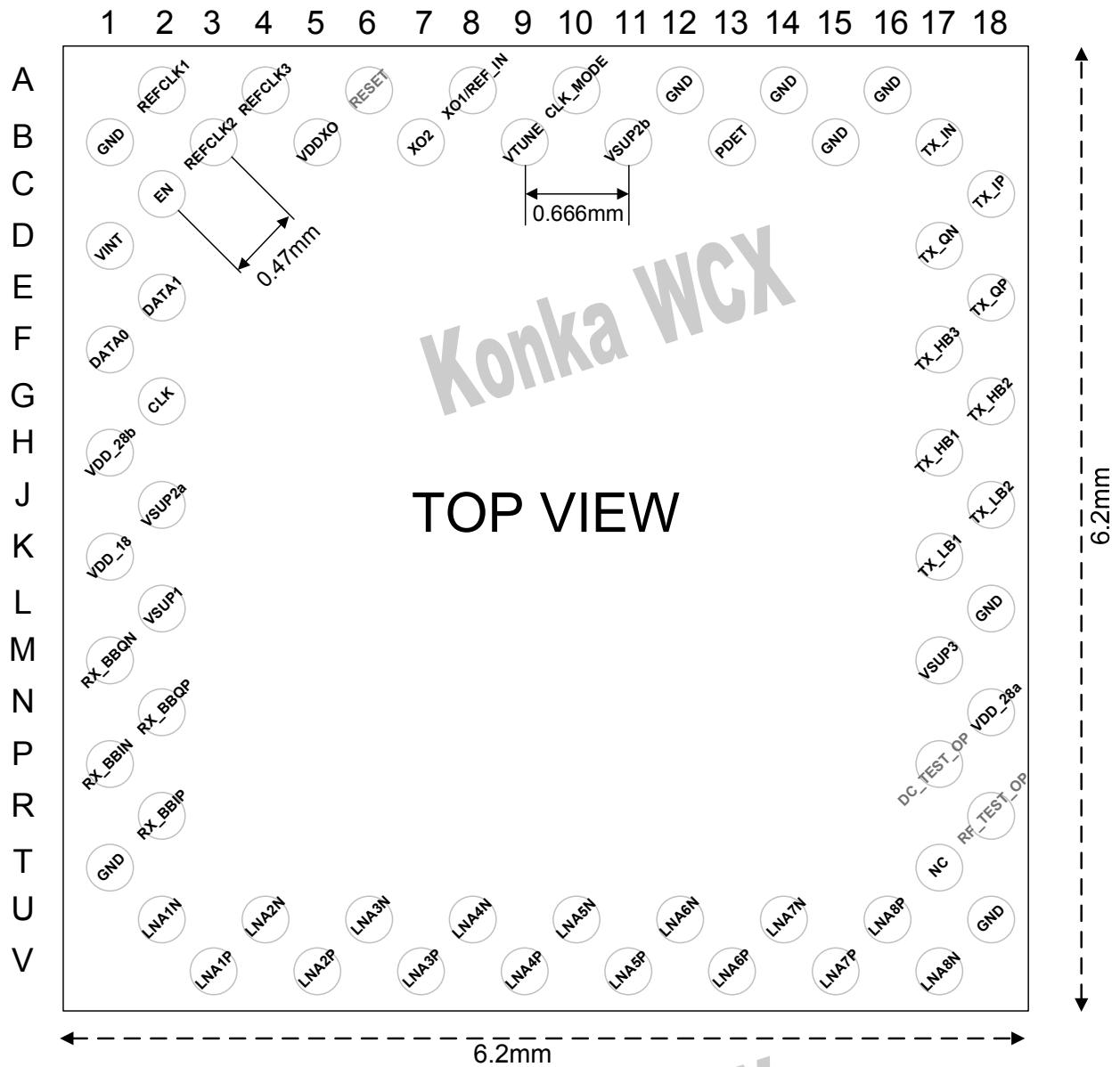


Figure 2



**Table 4 Pin Allocation / Function Description**

| Pin | Name      | Description   | Pin | Name    | Description                         |
|-----|-----------|---|-----|---------|-------------------------------------|
| A2  | REFCLK1   | Reference Clock Buffer #1 main for digital baseband | K1  | VDD_18  | Regulated supply for IC             |
| A4  | REFCLK3   | Reference Clock Buffer #3                           | K17 | TX_LB1  | Tx Low band Driver #1               |
| A6  | NC        | No connect  | L2  | VSUP1   | Internal Supply (ext. cap)          |
| A8  | XO1/REFIN | Crystal Pin #1 or Ref Clock Input                   | L18 | GND     | Ground; connect to GND plane on PCB |
| A10 | CLK_MODE  | Select DCXO or VCTCXO                               | M1  | RX_BBQN | Rx Baseband Output – Q Channel      |
| A12 | GND       | Ground; connect to GND plane on PCB                 | M17 | VSUP3   | Internal Supply (ext. cap)          |
| A14 | GND       | Ground; connect to GND plane on PCB                 | N2  | RX_BBQP | Rx Baseband Output – Q Channel      |
| A16 | GND       | Ground; connect to GND plane on PCB                 | N18 | VDD_28a | Regulated supply for IC             |
| B1  | GND       | Ground; connect to GND plane on PCB                 | P1  | RX_BBIN | Rx Baseband Output – I Channel      |
| B3  | REFCLK2   | Reference Clock Buffer #2                           | P17 | NC      | No connect                          |
| B5  | VDDXO     | Regulated supply for VCXO/DCXO                      | R2  | RX_BBIP | Rx Baseband Output – I Channel      |
| B7  | XO2       | Crystal Pin #2                                      | R18 | NC      | No connect                          |
| B9  | VTUNE     | AFCDAC Output                                       | T1  | GND     | Ground; connect to GND plane on PCB |
| B11 | VSUP2b    | Internal Supply (ext. cap)                          | T17 | NC      | No Connect                          |
| B13 | PDET      | Power Detector Input                                | U2  | LNA1N   | Rx Path #1 Input                    |
| B15 | GND       | Ground; connect to GND plane on PCB                 | U4  | LNA2N   | Rx Path #2 Input                    |
| B17 | TX_IN     | Tx Baseband Input – I Channel                       | U6  | LNA3N   | Rx Path #3 Input                    |
| C2  | EN        | Serial Interface Enable (BSI)                       | U8  | LNA4N   | Rx Path #4 Input                    |
| C18 | TX_IP     | Tx Baseband Input – I Channel                       | U10 | LNA5N   | Rx Path #5 Input                    |
| D1  | VINT      | Serial interface control logic                      | U12 | LNA6N   | Rx Path #6 Input                    |
| D17 | TX_QN     | Tx Baseband Input – Q Channel                       | U14 | LNA7N   | Rx Path #7 Input                    |
| E2  | DATA1     | Serial Data I/O (BSI)                               | U16 | LNA8P   | Rx Path #8 Input                    |
| E18 | TX_QP     | Tx Baseband Input –Q Channel                        | U18 | GND     | Ground; connect to GND plane on PCB |
| F11 | DATA0     | Serial Data I/O (BSI)                               | V3  | LNA1P   | Rx Path #1 Input                    |
| F17 | TX_HB3    | Tx High band Driver #3                              | V5  | LNA2P   | Rx Path #2 Input                    |
| G2  | CLK       | Serial Interface Clock (BSI)                        | V7  | LNA3P   | Rx Path #3 Input                    |
| G18 | TX_HB2    | Tx High band Driver #2                              | V9  | LNA4P   | Rx Path #4 Input                    |
| H1  | VDD_28b   | Regulated supply for IC                             | V11 | LNA5P   | Rx Path #5 Input                    |
| H17 | TX_HB1    | Tx High band Driver #1 (2G only)                    | V13 | LNA6P   | Rx Path #6 Input                    |
| J2  | VSUP2a    | Internal Supply (ext. cap)                          | V15 | LNA7P   | Rx Path #7 Input                    |
| J18 | TX_LB2    | Tx Low band Driver #2 (2G only)                     | V17 | LNA8N   | Rx Path #8 Input                    |

notes

1. VSUP2a and VSUP2b should be shorted on the PCB
2. VDD\_28a and VDD\_28b should be shorted on the PCB
3. Pin T17 is recommended a 'No Connect' pin to balance parasitics on the RF Input pins
4. CLK\_MODE:  
 GND = Internal DCXO (Crystal mode)  
 Floating or connect to VDDXO = External Clock (VCTCXO)

## TRANSCEIVER PIN CONFIGURATION

### RECEIVER FRONT-END MAPPING

Each of the eight independent LNA/mixer/divider are dedicated to either high (VCO divide-by-2) or low (VCO divide-by-4) band. Furthermore, even though the LNA's are identical, some recommended configurations are required since performance may be limited by board/package isolation.

**Table 5 Rx configuration**

| LNA # | High / Low | Configuration#1 | Configuration#2 | Configuration#3       |
|-------|------------|-----------------|-----------------|-----------------------|
| 1     | HB         | Band 2          | Band2/GSM1900   | Band 2                |
| 2     | LB         | Band 8          | Band8/GSM900    | Band 8                |
| 3     | HB         | Band 1          | Band 1          | Band 1                |
| 4     | LB         | Band 5          | Band5/GSM850    | Band 5                |
| 5     | HB         | GSM1900         | N/C             | Band 4                |
| 6     | HB         | GSM1800         | GSM1800         | GSM1800/1900 (Diplex) |
| 7     | LB         | GSM900          | N/C             | GSM900                |
| 8     | LB         | GSM850          | N/C             | GSM850                |

### TRANSMITTER FRONT-END MAPPING

Each of the five independent Tx output drivers are dedicated to either high (VCO divide-by-2) or low (VCO divide-by-4) band. Furthermore, two outputs (TX\_LB2/TX\_HB1) are dedicated to GSM/EDGE mode only, and the remaining three outputs are multi-mode (MM = '3G and GSM/EDGE').

**Table 6 Tx Configuration#1**

| Tx Output | GSM850/900 | GSM1800/1900 | B5/B8 | B1/B2/B3/B4 | Notes                             |
|-----------|------------|--------------|-------|-------------|-----------------------------------|
| TX_LB1    |            |              | ✓     |             | Single Mode WCDMA or Multimode PA |
| TX_LB2    | ✓          |              |       |             | Single Mode GSM/EDGE PA           |
| TX_HB1    |            | ✓            |       |             | Single Mode GSM/EDGE PA           |
| TX_HB2    |            |              |       | ✓           | Single Mode WCDMA or Multimode PA |
| TX_HB3    |            |              |       | ✓           | Single Mode WCDMA or Multimode PA |

**Table 7 Tx Configuration#2**

| Tx Output | GSM850/900 | GSM1800/1900 | B5/B8 | B1/B2/B3/B4 | Notes                             |
|-----------|------------|--------------|-------|-------------|-----------------------------------|
| TX_LB1    | ✓          |              | ✓     |             | Single Mode WCDMA or Multimode PA |
| TX_LB2    |            |              |       |             | Single Mode GSM/EDGE PA           |
| TX_HB1    |            |              |       |             | Single Mode GSM/EDGE PA           |
| TX_HB2    |            | ✓            |       | ✓           | Single Mode WCDMA or Multimode PA |
| TX_HB3    |            |              |       |             | Single Mode WCDMA or Multimode PA |

## ELECTRICAL CHARACTERISTICS

The Electrical Characteristics defined are valid for the Operating Conditions specified in Table 1, receiver pin configuration#1, and transmitter pin configuration#1, unless otherwise described. For ABB gain blocks settings based on a specific ABB gain. The dc-dc converter supplying V<sub>DD\_18</sub> is assumed to have 90% efficiency and operates from a nominal battery voltage, V<sub>bat</sub> ~ 3.6V.

Typical specifications are for register settings are mid-band channel frequencies, and recommended operating conditions. Min/Max specifications are for Extreme operating voltage and temperature conditions, unless otherwise stated.

### DC & VOLTAGE REGULATORS

Table 8

| Parameter  | Min | Typ | Max  | Unit | Test Conditions / Comments           |
|--|-----|-----|------|------|--------------------------------------|
| Idle mode  |     | 11  |      | μA   | V <sub>INT</sub> on; All else off    |
| <b>Equivalent Battery Supply Current</b> <sup>3)</sup> |     |     |      |      | VDD_18 & VDD_28                      |
| Rx Alert   |     | 3.3 | 4    | mA   | All Rx power domain LDOs enabled     |
| Rx On  |     |     |      |      | RX signal path fully enabled; Tx off |
| 3G mode, max gain                                      |     | 38  | 48   | mA   | LNA HI gain/ ABB gain: 32dB          |
| 3G mode, med gain                                      |     | 31  | 40   | mA   | LNA MED gain/ ABB gain: 14dB         |
| 3G mode, low gain                                      |     | 28  | 35   | mA   | LNA LOW gain/ ABB gain: -7dB         |
| GGE mode, max gain                                     |     | 40  | 50   | mA   | LNA HI gain/ ABB gain: 32dB          |
| GGE mode, med gain                                     |     | 33  | 41   | mA   | LNA MED gain/ ABB gain: 14dB         |
| GGE mode, low gain                                     |     | 30  | 37.5 | mA   | LNA LOW gain/ ABB gain: -7dB         |
| Tx Alert   |     | 2   | 3    | mA   | All Tx power domain LDOs enabled     |
| Tx (HB) On   |     |     |      |      | Tx high-band signal path on; Rx off  |
| WCDMA mode @ Pout = +4.5dBm                            |     | 92  | 112  | mA   | 12.2k UL ref ch. (187mVd rms I/Q)    |
| WCDMA mode @ Pout = +2.5dBm                            |     | 91  | 110  | mA   | 12.2k UL ref ch. (187mVd rms I/Q)    |
| WCDMA mode @ Pout = -10dBm                             |     | 51  | 62   | mA   | 12.2k UL ref ch. (187mVd rms I/Q)    |
| WCDMA mode @ Pout ≤ -58dBm                             |     | 34  | 43   | mA   | 12.2k UL ref ch. (187mVd rms I/Q)    |
| GMSK mode  |     | 35  | 44   | mA   | TX_HB1 output                        |
| 8PSK mode @ Pout = -2.5dBm                             |     | 64  | 80   | mA   | TX_HB1 output; (180mVd rms I/Q)      |
| MMMB GMSK mode   |     | 94  |      | mA   | TYP output power; RF gain = 1        |
| MMMB 8PSK mode @ Pout = +3.5dBm                        |     | 83  | 104  | mA   |                                      |
| Tx (LB) On   |     |     |      |      | Tx low-band signal path on; Rx off   |
| WCDMA mode @ Pout = +2.5dBm                            |     | 75  | 94   | mA   | 12.2k UL ref ch. (187mVd rms I/Q)    |
| WCDMA mode @ Pout = -10dBm                             |     | 40  | 50   | mA   | 12.2k UL ref ch. (187mVd rms I/Q)    |
| WCDMA mode @ Pout ≤ -58dBm                             |     | 34  | 43   | mA   | 12.2k UL ref ch. (187mVd rms I/Q)    |
| GMSK mode  |     | 36  | 45   | mA   | TX_LB2 output                        |
| 8PSK mode @ Pout = +0.5dBm                             |     | 71  | 89   | mA   | TX_LB2 output; (180mVd rms I/Q)      |
| MMMB GMSK mode   |     | 87  |      | mA   | TYP output power; RF gain = 1        |
| MMMB 8PSK mode @ Pout = +4.5dBm                        |     | 90  | 110  | mA   |                                      |

$$^3) \text{ equivalent\_battery\_current} = I_{dd}(VDD\_28) + I_{dd}(VDD\_18) \times \frac{1.8V}{3.6V} \times \frac{1}{0.9}$$

Table 9

| Parameter                   | Min | Typ | Max | Unit | Test Conditions / Comments  |
|-----------------------------|-----|-----|-----|------|---|
| <b>VDDXO Supply Current</b> |     |     |     |      |   |
| External clock mode         |     | 2.2 |     | mA   | REFCLK1 output enabled with DS load condition; AFC DAC turned off |
| DCXO mode                   |     | 3.5 |     | mA   | REFCLK1 output enabled with DS load condition; AFC DAC turned off |

**RECEIVER SYSTEM**

All receiver characteristics are applicable for all RX frequency bands when operated under the recommended operating conditions and receiver pin configuration#1, unless stated otherwise. Receiver’s differential input ports are matched to 100Ω (3G) / 100Ω (GGE) characteristic impedance ( $Z_0$ ), with all power levels (in dBm) referenced to  $Z_0$ . The BB I/Q output ports are presented each with a differential load equivalent to 32kΩ||5pF. The reference oscillator’s frequency used for the on-chip PLL is 26MHz. For ABB gain blocks settings based on a specific ABB gain.

Typical specifications are for register settings mid-band channel frequency, and recommended operating conditions. Min/Max specifications are for Extreme operating voltage and temperature conditions, unless otherwise stated.

**Table 10**

| Parameter   | Symbol          | Min | Typ | Max | Unit | Test Conditions / Comments  |
|---|-----------------|-----|-----|-----|------|---|
| <b>3G Receiver</b>                                    |                 |     |     |     |      |   |
| Input Return Loss                                     | $S_{11}$        |     | -10 |     | dB   | Ref. plane ( $Z_0$ ) at matching components                                     |
| Voltage gain: Max. (HB)                               | $G_{V,max}$     | 67  | 70  | 72  | dB   | LNA HI gain; $G_{ABB}= 32dB$  |
| Max (LB)  |                 | 66  | 69  | 71  | dB   |   |
| Voltage gain: Mid. (HB)                               | $G_{V,mid}$     | 38  | 41  | 43  | dB   | LNA MED gain; $G_{ABB}= 14dB$   |
| Voltage gain: Min. (HB)                               | $G_{V,min}$     | 3   | 6   | 8   | dB   | LNA LOW gain; $G_{ABB}= -7dB$   |
| Min. (LB)   |                 | 5   | 8   | 10  | dB   |   |
| DSB Noise Figure (HB)                                 | $NF_{HI}$       |     | 2.5 | 3.9 | dB   | All frequency channels; LNA HI gain;  |
| (LB)  |                 |     | 2.6 | 4.0 | dB   | $G_{ABB}= 29dB$   |
| DSB Noise Figure, Mid. gain                           | $NF_{MID}$      |     | 13  | 16  | dB   | LNA MED gain; $G_{ABB}= 14dB$   |
| Rx Composite EVM*                                     | $EVM_{Rx}$      |     |     |     |      | -63dBm desired signal; Rx gain = $G_{V,mid}$ ;                                  |
| (* not including digital baseband phase compensation) |                 |     | 5   | 8   | %    | // (HSDPA Hset-2 QPSK)  |
|   |                 |     | 6   | 9   | %    | // (HSDPA Hset-2 16QAM)   |
| Input IP3 (ACS1)                                      | $iIP_{3,ACS1}$  | -3  | 2   |     | dBm  | $df1= \pm 3.5M$ , $df2= \pm 6.5M$ ; -35dBm/tone; LNA MED gain; $G_{ABB}= 23dB$  |
| Input IP3 (ACS2)                                      | $iIP_{3,ACS2}$  | 0   | 5   |     | dBm  | $df1= \pm 3.5M$ , $df2= \pm 6.5M$ ; -20dBm/tone; LNA LOW gain; $G_{ABB}= 20dB$  |
| Input IP3 (10/20M) (HB)                               | $iIP_{3,IM}$    | -7  | -2  |     | dBm  | $df1= \pm 10.1MHz$ , $df2= \pm 20MHz$ //  |
| (LB)  |                 | -5  | 0   |     |      | -38dBm/tone; LNA HI gain; $G_{ABB}= 29dB$                                       |
| Input IP3 (NB_IM)                                     | $iIP_{3,NBIM}$  |     |     |     |      | -35dBm/tone; LNA HI gain; $G_{ABB}= 17dB$                                       |
| (HB)  |                 | -7  | -2  |     | dBm  | $df1/2= \pm 3.5MHz/ \pm 5.9MHz$ (band II/V/X);                                  |
| (LB)  |                 | -4  | 1   |     | dBm  | $df1/2= \pm 3.6MHz/ \pm 6.0MHz$ (band III/ VIII)                                |
| Input IP3 (GMSK w Tx Blocker)                         | $iIP_{3,NBwTx}$ |     |     |     |      | -35dBm/tone; LNA MED gain; $G_{ABB}= 29dB$                                      |
| Band II/V/X   |                 | -2  | 3   |     | dBm  | $df1= \pm 2.7MHz$ , $f2/f3=f_{Tx}-1.1/+1.1MHz$                                  |
| Band III/VIII   |                 | -2  | 3   |     | dBm  | $df1= \pm 2.8MHz$ , $f2/f3=f_{Tx}-1.1/+1.1MHz$                                  |
| Input IP3 (Out of Band blocker)                       | $iIP_{3,OBwTx}$ |     |     |     |      | LNA HI gain; $G_{ABB}= 29dB$  |
| Band I  |                 | -7  | -3  |     | dBm  | 2024.9M/ -38dBm, 1930M/ -28dBm  |
| Band II   |                 | -7  | -3  |     | dBm  | 1830.2M/ -38dBm, 1910M/ -28dBm  |
| Band V  |                 | -4  | 0   |     | dBm  | 784.2M/ -41dBm, 829M/ -31dBm  |
| Band VIII   |                 | -4  | 0   |     | dBm  | 840.2M/ -41dBm, 885M/ -31dBm  |
| Input IP2 (ACS2)                                      | $iIP_{2,ACS2}$  | 50  | >60 |     | dBm  | $df1= \pm 4.5M$ , $df2= \pm 5.5M$ ; -20dBm/tone; LNA LOW gain; $G_{ABB}= 20dB$  |
| Input IP2 (@15M inband blocker offset)                | $iIP_{2,IB15}$  | 40  | 50  |     | dBm  | $df1= \pm 14.5M$ , $df2= \pm 15.5M$ ; -27dBm/tone; LNA HI gain; $G_{ABB}= 26dB$ |
| Input IP2 (@ Tx blocker offset)                       | $iIP_{2,Tx}$    |     |     |     |      |   |
| (HB)  |                 | 45  | 55  |     | dBm  | $f1= \pm(f_{Tx}-0.5M)$ ; $f2= \pm(f_{Tx}+0.5M)$ ;                               |
| (LB)  |                 | 45  | 55  |     | dBm  | -27dBm/tone; LNA HI gain; $G_{ABB}= 29dB$                                       |
| Input-1dB compression                                 | $IP_{-1dB}$     | -9  | -5  |     | dBm  | LNA LOW gain; $G_{ABB}= -7dB$   |

| Parameter   | Symbol                  | Min  | Typ  | Max  | Unit | Test Conditions / Comments  |
|---|-------------------------|------|------|------|------|---|
| Input-1dB gain compression (ACS2)   | IP <sub>-1dB,ACS2</sub> | -12  | -8   |      | dBm  | Blocker level that results in 1dB gain reduction at desired signal; LNA LOW gain; G <sub>ABB</sub> = 20dB |
| Input-1dB gain compression (Inband Blocker @ 15M offset)                      | IP <sub>-1dB,IB15</sub> | -19  | -15  |      | dBm  | Blocker level that results in 1dB gain reduction at desired signal; LNA HI gain; G <sub>ABB</sub> = 26dB  |
| Input-1dB gain compression (GMSK blocker @ 2.7M offset; band II/III/V/VIII/X) | IP <sub>-1dB,GMSK</sub> | -38  | -34  |      | dBm  | Blocker level that results in 1dB gain reduction at desired signal; LNA MED gain; G <sub>ABB</sub> = 29dB |
| Input-1dB gain compression (Tx blocker)                                       | IP <sub>-1dB,TX</sub>   | -19  | -15  |      | dBm  | Blocker level that results in 1dB gain reduction at desired signal; LNA HI gain; G <sub>ABB</sub> = 29dB  |
| Uncal. I/Q phase mismatch   | ΔΦ <sub>IQ,RX</sub>     |      |      | ±2   | deg  | Un-calibrated spec.; LNA MED gain //  |
| Uncal. I/Q amplitude mismatch   | ΔA <sub>IQ,RX</sub>     |      |      | ±0.5 | dB   | G <sub>ABB</sub> = 17dB; BB tone freq. = 200kHz   |
| Quadrature phase mismatch   | ΔΦ <sub>IQ,RX</sub>     |      |      | ±0.5 | deg  | Calibrated spec. using TTG RF tone //   |
| Quadrature amplitude mismatch   | ΔA <sub>IQ,RX</sub>     |      |      | ±0.1 | dB   | LNA MED gain; G <sub>ABB</sub> = 17dB; BB tone freq. = 200kHz   |
| <b>3G Receiver Analog Baseband section</b>                                    |                         |      |      |      |      |   |
| DC Common Mode Level  | V <sub>RX,DCCM</sub>    | 1.08 | 1.2  | 1.32 | V    |   |
| Output-1dB Compression  | OP <sub>-1dB</sub>      | 1.7  | 1.9  | 2.1  | Vpd  | LNA HI gain; G <sub>ABB</sub> = 29dB  |
| Gain step variation   | ΔG <sub>RX,3dB</sub>    | -0.2 |      | 0.2  | dB   | 3dB gain step from any gain setting   |
|   | ΔG <sub>RX,XdB</sub>    | -0.5 |      | 0.5  | dB   | Any gain change   |
| Baseband filter   |                         |      |      |      |      |   |
| 3dB corner frequency  | A <sub>-3dB</sub>       | 2.11 | 2.23 |      | MHz  | After corner frequency calibration  |
| Stopband attenuation  |                         |      |      |      |      |   |
| 2.7/2.8M offset (GMSK)  | A <sub>GSM2.7M</sub>    | 6    | 8    |      | dB   | Integrated over 200kHz BW at 2.7/2.8M   |
| 3.5/3.6M offset (CW)  | A <sub>3.5M</sub>       | 14   | 17   |      | dB   | At 3.5/3.6M   |
| 5.9/6.0M offset (GMSK)  | A <sub>GSM5.9M</sub>    | 30   | 33   |      | dB   | Integrated over 200kHz BW at 5.9/6.0M   |
| 5M offset (WCDMA)   | A <sub>W5M</sub>        | 18   | 22   |      | dB   | Integrated over 3.84M BW at 5M  |
| 10M offset (WCDMA)  | A <sub>W10M</sub>       | 45   | 49   |      | dB   | Integrated over 3.84M BW at 10M   |
| 15M offset (WCDMA)  | A <sub>W15M</sub>       | 65   | 69   |      | dB   | Integrated over 3.84M BW at 15M   |

Table 11

| Parameter                         | Symbol                  | Min | Typ | Max | Unit | Test Conditions / Comments   |
|-----------------------------------|-------------------------|-----|-----|-----|------|--|
| <b>GGE Receiver</b>               |                         |     |     |     |      |  |
| Input Return Loss                 | S <sub>11</sub>         |     | -10 |     | dB   | Ref. plane (Z <sub>0</sub> ) at matching components  |
| Voltage gain: Max. (HB)           | G <sub>V,max</sub>      | 67  | 70  | 72  | dB   | LNA HI gain/ G <sub>ABB</sub> = 32dB   |
| Max (LB)                          |                         | 66  | 69  | 71  | dB   |  |
| Voltage gain: Mid.                | G <sub>V,mid</sub>      | 38  | 41  | 43  | dB   | LNA MED gain/ G <sub>ABB</sub> = 14dB  |
| Voltage gain: Min.                | G <sub>V,min</sub>      | 3   | 6   | 9   | dB   | LNA LOW gain/ G <sub>ABB</sub> = -7dB  |
| DSB Noise Figure (HB)             | NF <sub>HI</sub>        |     | 2.3 | 3.4 | dB   | All frequency channels; LNA HI gain;   |
| (LB)                              |                         |     | 2.5 | 3.6 | dB   | G <sub>ABB</sub> = 29dB  |
| Input IP3 (HB)                    | iIP <sub>3,IM</sub>     | -5  | -1  |     | dBm  | df1= ±0.81MHz, df2= ±1.6MHz;   |
| (LB)                              |                         | -3  | 1   |     | dBm  | -41dBm/tone; LNA HI gain; G <sub>ABB</sub> = 29dB  |
| Input IP2 (AM detection) (HB)     | iIP <sub>2,AM</sub>     | 45  | 55  |     | dBm  | df1= ±5.98MHz, df2= ±6.02MHz;  |
| (LB)                              |                         | 50  | 60  |     | dBm  | -27dBm/tone; LNA HI gain; G <sub>ABB</sub> = 29dB  |
| Input-1dB compression             | IP <sub>-1dB</sub>      | -9  | -5  |     | dBm  | LNA LOW gain; G <sub>ABB</sub> = -7dB  |
| Input-1dB gain compression (AC11) | IP <sub>-1dB,AC11</sub> | -31 | -27 |     | dBm  | Blocker level that results in 1dB gain reduction at desired signal; LNA HI gain; G <sub>ABB</sub> = 14dB |

| Parameter   | Symbol                  | Min  | Typ | Max  | Unit | Test Conditions / Comments   |
|---|-------------------------|------|-----|------|------|--|
| Input-1dB gain compression (ACI2)                   | IP <sub>-1dB,ACI2</sub> | -32  | -28 |      | dBm  | Blocker level that results in 1dB gain reduction at desired signal; LNA HI gain; G <sub>ABB</sub> = 20dB |
| Input-1dB gain compression (CW Blocker 0.8M offset) | IP <sub>-1dB,0.8M</sub> | -30  | -26 |      | dBm  | Blocker level that results in 1dB gain reduction at desired signal; LNA HI gain; G <sub>ABB</sub> = 29dB |
| Input-1dB gain compression (CW Blocker 3M offset)   | IP <sub>-1dB,3M</sub>   | -21  | -17 |      | dBm  | Blocker level that results in 1dB gain reduction at desired signal; LNA HI gain; G <sub>ABB</sub> = 29dB |
| 2-Rx Suppression                                    | H <sub>OOB_2RX</sub>    | 37   | 55  |      | dB   | LNA HI gain; G <sub>ABB</sub> = 29dB   |
| 3-Rx Suppression (HB)                               | H <sub>OOB_3RX</sub>    | 20   | 25  |      | dB   | LNA HI gain; G <sub>ABB</sub> = 29dB   |
| (LB)  |                         | 18   | 23  |      | dB   | LNA HI gain; G <sub>ABB</sub> = 29dB   |
| 5-Rx Suppression (LB)                               | H <sub>OOB_5RX</sub>    | 26   | 35  |      | dB   | LNA HI gain; G <sub>ABB</sub> = 29dB   |
| Uncal. I/Q phase mismatch                           | $\Delta\Phi_{IQ\_RX}$   |      |     | ±2   | deg  | Un-calibrated spec.; LNA MED gain//  |
| Uncal. I/Q amplitude mismatch                       | $\Delta A_{IQ\_RX}$     |      |     | ±0.5 | dB   | G <sub>ABB</sub> = 17dB; BB tone freq. = 200kHz  |
| Quadrature phase mismatch                           | $\Delta\Phi_{IQ\_RX}$   |      |     | ±0.5 | deg  | Calibrated spec. using TTG RF tone //  |
| Quadrature amplitude mismatch                       | $\Delta A_{IQ\_RX}$     |      |     | ±0.1 | dB   | LNA MED gain; G <sub>ABB</sub> = 17dB; BB tone freq. = 200kHz  |
| <b>GGE Receiver Analog Baseband section</b>         |                         |      |     |      |      |  |
| DC Common Mode Level                                | V <sub>RX_DCCM</sub>    | 1.08 | 1.2 | 1.32 | V    |  |
| Output-1dB Compression                              | OP <sub>-1dB</sub>      | 1.7  | 1.9 | 2.1  | Vpd  | LNA HI gain; G <sub>ABB</sub> = 29dB   |
| Gain step variation                                 | $\Delta G_{RX\_3dB}$    | -0.2 |     | 0.2  | dB   | 3dB gain step from any gain setting  |
|   | $\Delta G_{RX\_XdB}$    | -0.5 |     | 0.5  | dB   | Any gain change  |
| Baseband filter                                     |                         |      |     |      |      |  |
| 3dB corner frequency                                | A <sub>-3dB</sub>       | 148  | 156 |      | kHz  | After calibration  |
| Stopband attenuation                                |                         |      |     |      |      |  |
| ACI2  | A <sub>ACI1</sub>       | 22   | 26  |      | dB   | 400kHz offset (BW=200kHz)  |
| ACI3  | A <sub>ACI2</sub>       | 35   | 39  |      | dB   | 600kHz offset (BW=200kHz)  |
| 800kHz offset (CW)                                  | A <sub>0.8M</sub>       | 44   | 49  |      | dB   | At 800kHz  |
| 1.6MHz offset (CW)                                  | A <sub>1.6M</sub>       | 65   | 75  |      | dB   | At 1.6M  |
| 3.0MHz offset (CW)                                  | A <sub>3.0M</sub>       |      | >90 |      | dB   | At 3.0M  |

**TRANSMITTER SYSTEM**

All transmitter characteristics are applicable for all TX frequency bands when operated under the recommended operating conditions and transmitter pin configuration#1, unless stated otherwise. Measured with 50ohm load at driver output; Input at BB is DC coupled (High Zin). In 3G and GGE modes, I/Q inputs are driven each with 185mVrms DIFF signal (WCDMA UL 12.2kbps reference channel) and 180mVrms (8PSK), respectively. The reference oscillator used with the on-chip PLL is 26MHz.

Typical specifications are for mid-band channel frequency, and recommended operating conditions. Min/Max specifications are for Extreme operating voltage and temperature conditions, unless otherwise stated.

**Table 12**

| Parameter                    | Symbol           | Min | Typ  | Max  | Unit | Test Conditions / Comments  |
|------------------------------|------------------|-----|------|------|------|---|
| <b>3G Transmitter Output</b> |                  |     |      |      |      |   |
| Output Return Loss           | S <sub>22</sub>  |     | -12  | -10  | dB   | 50Ω load  |
| Max Output Power             |                  |     |      |      |      |   |
| All bands, except Band II    | P <sub>max</sub> | 2.5 |      |      | dBm  | Worst case ACLR, EVM, noise emissions, and spurious emissions specs. are met      |
| Band II only                 | P <sub>max</sub> | 4.5 |      |      | dBm  |   |
| Min Output Power             |                  |     |      |      |      |   |
| (HB)                         | P <sub>min</sub> |     |      | -82  | dBm  |   |
| (LB)                         | P <sub>min</sub> |     |      | -81  | dBm  |   |
| RF output Frequency response | ΔP               |     | ±0.2 | ±0.7 | dB   | P <sub>out</sub> = min.P <sub>max</sub>   |
| ACLR1                        |                  |     |      |      |      | ±5MHz offset;   |
| (HB)                         | ACLR1            |     | -48  | -43  | dBc  | P <sub>out</sub> = min.P <sub>max</sub>   |
| (LB)                         | ACLR1            |     | -50  | -41  | dBc  | P <sub>out</sub> = min.P <sub>max</sub>   |
| All bands                    | ACLR1            |     | -52  | -48  | dBc  | P <sub>out</sub> = min.P <sub>max</sub> - 11dB                                    |
| ACLR2                        | ACLR2            |     | -71  | -65  | dBc  | ±10MHz offset; P <sub>out</sub> = min.P <sub>max</sub>                            |
| EVM                          |                  |     |      |      |      | Measured over 1 slot/2560chips, after Tx I/Q imbalance and LO leakage calibration |
| (HB)                         | EVM              |     | 2.0  | 3.0  | %    | P <sub>out</sub> = min.P <sub>max</sub>   |
|                              |                  |     | 2.0  | 3.0  | %    | P <sub>out</sub> = min.P <sub>max</sub> -11dB                                     |
| (LB)                         | EVM              |     | 1.5  | 2.3  | %    | P <sub>out</sub> = min.P <sub>max</sub>   |
|                              |                  |     | 1.5  | 2.3  | %    | P <sub>out</sub> = min.P <sub>max</sub> -11dB                                     |
| Spectrum Emission Mask       | SEM              |     |      |      |      | P <sub>out</sub> = min.P <sub>max</sub> ; 3.5M offset in 30kHz BW                 |
| (HB)                         |                  |     | -60  | -56  | dBc  | Note A  |
| (LB)                         |                  |     | -65  | -61  | dBc  | Note A  |
| Carrier Suppression          |                  |     |      | -20  | dBc  | P <sub>out</sub> ≥ min.P <sub>max</sub> -44dB; before calibration                 |
|                              |                  |     | -48  | -35  | dBc  | P <sub>out</sub> = min.P <sub>max</sub> ; after calibration                       |
|                              |                  |     | -39  | -31  | dBc  | P <sub>out</sub> = min.P <sub>max</sub> -44dB; after calibration                  |
| Sideband Suppression         |                  |     | -45  | -38  | dBc  | P <sub>out</sub> ≥ min.P <sub>max</sub> -44dB; after calibration                  |
| Harmonic Emissions in 1 MHz  |                  |     |      |      |      |   |
| 2 <sup>nd</sup> harmonic     |                  |     |      | -25  | dBc  | P <sub>out</sub> = min.P <sub>max</sub>   |
| 3 <sup>rd</sup> harmonic     |                  |     |      | -15  | dBc  | P <sub>out</sub> = min.P <sub>max</sub>   |
| 4 <sup>th</sup> harmonic     |                  |     |      | -25  | dBc  | P <sub>out</sub> = min.P <sub>max</sub>   |
| Ref. clock harmonics         |                  |     | -90  | -70  | dBc  | 52MHz; 104MHz; 208MHz   |

*Note A: NTC1: Nominal Test Conditions (Low, Mid, High frequency channels; +15C ... +35C ambient temperature; Vbat = 3.6 – 4.0V)*

| Parameter                     | Symbol | Min | Typ    | Max    | Unit   | Test Conditions / Comments  |
|-------------------------------|--------|-----|--------|--------|--------|---|
| Noise Emissions               |        |     |        |        |        |   |
| Band I, 12.5MHz offset        |        |     | -145   | -140   | dBc/Hz | Pout= min.P <sub>max</sub> ; Note A                                     |
| Band I, 40MHz offset          |        |     | -159   | -157   | dBc/Hz | Pout= min.P <sub>max</sub> ; measured at 1880M with fTx = 1920M; Note A |
| Band I, noise in Rx           |        |     | -162.5 | -159.5 | dBc/Hz | Pout= min.P <sub>max</sub> ; measured at 135M offset                    |
| Band II, noise in Rx          |        |     | -162   | -160   | dBc/Hz | Pout = -9dBm; measured at 135M offset                                   |
| Band V/VI, noise in Rx        |        |     | -162   | -160   | dBc/Hz | Pout= min.P <sub>max</sub> ; measured at 80M offset                     |
| Band VIII, noise in Rx        |        |     | -162   | -160   | dBc/Hz | Pout = -6dBm; measured at 80M offset                                    |
|                               |        |     |        | -156   | dBc/Hz | Pout= min.P <sub>max</sub> ; measured at 45M offset                     |
|                               |        |     |        | -156   | dBc/Hz | Pout = -8.0dBm; measured at 45M offset                                  |
|                               |        |     |        | -156   | dBc/Hz | Pout= min.P <sub>max</sub> ; measured at 45M offset                     |
|                               |        |     |        | -156   | dBc/Hz | Pout = -6.5dBm; measured at 45M offset                                  |
| <b>3G Tx baseband section</b> |        |     |        |        |        |   |
| Baseband Filter               |        |     |        |        |        |   |
| Selectivity, 10MHz offset     |        | 10  | 20     |        | dB     | After frequency corner calibration                                      |
| Selectivity, 40MHz offset     |        |     | 55     |        | dB     | After frequency corner calibration                                      |
| <b>3G TX Gain Control</b>     |        |     |        |        |        |   |
| Gain control resolution       |        |     | 1/32   |        | dB     | Average of LSB steps  |
| Gain Control Step Accuracy    |        | 0.7 | 1.0    | 1.3    | dB     | Any 1dB step  |
|                               |        | 8.5 | 10     | 11.5   | dB     | Any 10dB step   |

Table 13

| Parameter                     | Symbol               | Min  | Typ | Max | Unit | Test Conditions / Comments  |
|-------------------------------|----------------------|------|-----|-----|------|---|
| <b>GGE Transmitter Output</b> |                      |      |     |     |      |   |
| Output Return Loss            | S <sub>22</sub>      |      | -12 | -10 | dB   | 50Ω load  |
| Max Output Power (GMSK)       |                      |      |     |     |      |   |
| 2G output, Mode1              | P <sub>max</sub>     | 1    | 3   | 5   | dBm  | GMSK Modulation, using DFM  |
| 2G output, Mode2, LB only     | P <sub>max</sub>     | 4    | 6   | 8   | dBm  | GMSK Modulation, using DFM  |
| MM output                     | P <sub>max</sub>     | 8    | 10  | 12  | dBm  | GMSK Modulation, using DFM  |
| Max Output Power (8PSK)       |                      |      |     |     |      |   |
| 2G output, LB                 | P <sub>max</sub>     | 0.5  |     |     | dBm  | Worst case ORFS, EVM, noise and spurious emissions specs. are met |
| 2G output, HB                 | P <sub>max</sub>     | -2.5 |     |     | dBm  |   |
| MM output, LB                 | P <sub>max</sub>     | 4.5  |     |     | dBm  |   |
| MM output, HB                 | P <sub>max</sub>     | 3.5  |     |     | dBm  |   |
| Minimum Output Power (8PSK)   |                      |      |     |     |      |   |
| 2G output, LB                 | P <sub>min</sub>     |      |     | -33 | dBm  |   |
| 2G output, HB                 | P <sub>min</sub>     |      |     | -38 | dBm  |   |
| MM output, LB                 | P <sub>min</sub>     |      |     | -27 | dBm  |   |
| MM output, HB                 | P <sub>min</sub>     |      |     | -32 | dBm  |   |
| ORFS (GMSK)                   |                      |      |     |     |      |   |
| 200kHz                        | ORFS <sub>200k</sub> |      | -36 | -33 | dB   | Pout= min.P <sub>max</sub> ; BW=30kHz                             |
| 400kHz                        | ORFS <sub>400k</sub> |      | -66 | -63 | dB   | Pout= min.P <sub>max</sub> ; BW=30kHz                             |
| ORFS (8PSK)                   |                      |      |     |     |      |   |
| 200kHz                        | ORFS <sub>200k</sub> |      | -40 | -36 | dB   | Pout= min.P <sub>max</sub> ; BW=30kHz                             |
| 400kHz                        | ORFS <sub>400k</sub> |      | -65 | -62 | dB   | Pout= min.P <sub>max</sub> ; BW=30kHz                             |



| Parameter                              | Symbol        | Min    | Typ    | Max | Unit   | Test Conditions / Comments               |
|--|---------------|--------|--------|-----|--------|--|
| Modulation accuracy (GMSK)             |               |        |        |     |        |  |
| RMS phase error, LB                    | $\Phi_{RMS}$  |        | 1.2    | 3.0 | deg    | Pout= min.Pmax                           |
| RMS phase error, HB                    |               |        | 1.3    | 3.0 | deg    | Pout= min.Pmax                           |
| PEAK phase error, LB                   | $\Phi_{Peak}$ |        | 3.0    | 6.0 | deg    | Pout= min.Pmax                           |
| PEAK phase error, HB                   |               |        | 4.0    | 8.0 | deg    | Pout= min.Pmax                           |
| Modulation accuracy (8PSK)             |               |        |        |     |        |  |
| RMS EVM, LB                            | $EVM_{RMS}$   |        | 2.0    | 3.0 | %      | Pout= min.Pmax                           |
| RMS EVM, HB                            |               |        | 2.5    | 3.8 | %      | Pout= min.Pmax                           |
| Peak EVM, LB                           | $EVM_{Pk}$    |        | 6      | 10  | %      | Pout= min.Pmax                           |
| Peak EVM, HB                           |               |        | 8      | 12  | %      | Pout= min.Pmax                           |
| Origin offset suppression              | OOS           |        |        | -20 | dB     | 8PSK; Pout ≥ Pmin; before calibration    |
|  | OOS           |        | -40    | -35 | dB     | 8PSK; Pout = min.Pmax; after calibration |
|  | OOS           |        | -39    | -31 | dB     | 8PSK; Pout = Pmin; after calibration     |
| Sideband Suppression                   |               |        | -45    | -38 | dBc    | Pout ≥ Pmin; after calibration           |
| Tx Noise Emissions (GMSK)              |               |        |        |     |        |  |
| 20MHz offset, LB                       |               | -165.8 | -163   |     | dBc/Hz | Pout= min.Pmax; Note A                   |
| 20MHz offset, HB                       |               | -159   | -156   |     | dBc/Hz | Pout= min.Pmax; Note A                   |
| 32MHz offset, LB                       |               | -166.5 | -165   |     | dBc/Hz | Pout= min.Pmax; Note B                   |
| 32MHz offset, HB                       |               | -162   | -159   |     | dBc/Hz | Pout= min.Pmax; Note B                   |
| Tx Noise Emissions <sup>1</sup> (8PSK) |               |        |        |     |        | 2G Output                                |
| 20MHz offset, LB, Pout <sup>1</sup>    |               | -159   | -157   |     | dBc/Hz | Pout = -4dBm; Note A                     |
| Pout <sup>2</sup>                      |               |        | -163.5 |     | dBm/Hz | Pout ≤ -6.5dBm                           |
| 20MHz offset, HB, Pout <sup>1</sup>    |               | -154   | -152   |     | dBc/Hz | Pout = -7dBm; Note A                     |
| Pout <sup>2</sup>                      |               |        | -161.5 |     | dBm/Hz | Pout ≤ -9.5dBm                           |
| 32MHz offset, LB, Pout <sup>1</sup>    |               | -160.5 | -158   |     | dBc/Hz | Pout = -4dBm; Note B                     |
| Pout <sup>2</sup>                      |               |        | -164.5 |     | dBm/Hz | Pout ≤ -6.5dBm                           |
| 32MHz offset, HB, Pout <sup>1</sup>    |               | -155.5 | -153   |     | dBc/Hz | Pout = -7dBm; Note B                     |
| Pout <sup>2</sup>                      |               |        | -162.5 |     | dBm/Hz | Pout ≤ -9.5dBm                           |
| Tx Noise Emissions <sup>2</sup> (8PSK) |               |        |        |     |        | MM Output                                |
| 20MHz offset, LB, Pout <sup>1</sup>    |               | -162   | -158.5 |     | dBc/Hz | Pout = 0dBm; Note A                      |
| Pout <sup>2</sup>                      |               |        | -161   |     | dBm/Hz | Pout ≤ -2.5dBm                           |
| 20MHz offset, HB, Pout <sup>1</sup>    |               | -157   | -153.5 |     | dBc/Hz | Pout = -1dBm; Note A                     |
| Pout <sup>2</sup>                      |               |        | -157   |     | dBm/Hz | Pout ≤ -3.5dBm                           |
| 32MHz offset, LB, Pout <sup>1</sup>    |               | -162   | -158.5 |     | dBc/Hz | Pout = 0dBm; Note B                      |
| Pout <sup>2</sup>                      |               |        | -161   |     | dBm/Hz | Pout ≤ -2.5dBm                           |
| 32MHz offset, HB, Pout <sup>1</sup>    |               | -159   | -155.5 |     | dBc/Hz | Pout = -1dBm; Note B                     |
| Pout <sup>2</sup>                      |               |        | -159   |     | dBm/Hz | Pout ≤ -3.5dBm                           |
| Tx Spurious Emissions                  |               |        |        |     |        |  |
| 2 <sup>nd</sup> harmonic               |               |        |        | -25 | dBc    | Pout= min.Pmax                           |
| 3 <sup>rd</sup> harmonic               |               |        |        | -13 | dBc    | Pout= min.Pmax                           |
| 4 <sup>th</sup> harmonic               |               |        |        | -25 | dBc    | Pout= min.Pmax                           |
| <b>8PSK Tx baseband section</b>        |               |        |        |     |        |  |
| Baseband Filter                        |               |        |        |     |        |  |
| Selectivity, 20MHz offset              |               |        | 26     |     | dB     |  |

Note A: NTC1: Nominal Test Conditions (Low, Mid, High frequency channels; +15C ... +35C ambient temperature; Vbat = 3.6 – 4.0V)

Note B: TTC: Typical Test Conditions (Mid frequency channel; +25C ambient temperature; Vbat = 3.7V)

**TRANSMIT POWER CONTROL**

**Table 14**

| Parameter             | Symbol               | Min  | Typ | Max  | Unit        | Test Conditions / Comments       |
|-----------------------|----------------------|------|-----|------|-------------|----------------------------------|
| <b>Power Detector</b> |                      |      |     |      |             |                                  |
| RF Input Frequency    | F <sub>det</sub>     | 824  |     | 1980 | MHz         |                                  |
| Input Return Loss     | S <sub>11</sub>      |      | -12 | -10  | dB          | Ref. impedance 50Ω               |
| Maximum Input Signal  | P <sub>det,max</sub> |      |     | 0    | dBm         | 1dB excursion from nominal slope |
| Minimum Input Signal  | P <sub>det,min</sub> | -50  |     |      | dBm         | 1dB excursion from nominal slope |
| Measurement Accuracy  |                      | -0.3 |     | 0.3  | dB          | 3-σ; WCDMA/ 8PSK only            |
| Temperature Stability |                      | -15  | 2   | 15   | mdB/<br>°C  | Averaged over -40 to 100°C range |
| Frequency response    |                      |      |     | ±10  | mdB/<br>MHz | Averaged over any supported band |
| Measurement time      |                      |      | 14  |      | μs          | With above Specifications        |

**SYNTHESIZERS AND REFERENCES**

**Table 15**

| Parameter                              | Symbol | Min | Typ   | Max  | Unit            | Test Conditions / Comments  |
|--|--------|-----|-------|------|-----------------|---|
| <b>Receiver Synthesizer</b>            |        |     |       |      |                 |   |
| Channel resolution                     |        |     | 25    |      | kHz             |   |
| Lock Time                              |        |     | 120   | 150  | μs              | Phase within 10° of final lock conditions; frequency error removed                              |
| <b>Transmitter Synthesizer</b>         |        |     |       |      |                 |   |
| Channel resolution                     |        |     | 3     |      | Hz              | 3G / GGE mode   |
| Lock Time                              |        |     | 120   | 150  | μs              | Phase within 10° of final lock conditions; frequency error removed                              |
| GMSK Lock Time                         |        |     |       | 200  | μs              | In DFM mode (inc. loop gain calibration) after register CW1 is written; frequency error removed |
| <b>Reference Input (XO1)</b>           |        |     |       |      |                 |   |
| Frequency                              |        |     | 26    |      | MHz             |   |
| <b>Reference Outputs (REFCLK1,2,3)</b> |        |     |       |      |                 |   |
| Frequency                              |        |     | 26    |      | MHz             | REFCLK pin  |
| Output Swing                           |        | 0.7 |       | 1.2  | V <sub>pp</sub> | Square wave (3kΩ    20 pF Load)   |
| Rise / Fall Time                       |        | 2.5 |       | 9    | ns              | 10% - 90% of signal swing (3kΩ    20 pF Load)   |
| Duty Cycle                             |        | 40  |       | 60   | %               | 50% Input duty cycle  |
| Harmonic rejection                     |        |     | <-25  | -22  | dBc             | 2 <sup>nd</sup> harmonic  |
|  |        |     |       | -10  | dBc             | 3 <sup>rd</sup> harmonic  |
|  |        |     |       | -30  | dBc             | 4 <sup>th</sup> harmonic  |
| SSB phase noise                        |        |     | <-138 | -131 | dBc/Hz          | 1kHz offset   |
|  |        |     | <-147 | -141 | dBc/Hz          | 10kHz offset  |
|  |        |     | <-150 | -144 | dBc/Hz          | 100kHz offset   |

Table 16

| Parameter                  | Symbol               | Min | Typ   | Max | Unit        | Test Conditions / Comments  |
|----------------------------|----------------------|-----|-------|-----|-------------|---|
| <b>DCXO</b>                |                      |     |       |     |             |   |
| Center operating frequency | F <sub>DCXO</sub>    |     | 26    |     | MHz         | Square wave in high driving mode<br><br>CDAC from 0 to 255<br>CAFC from 0 to 8191<br><br>CAFC from 0 to 8191; CAFC from 8191 to 0; Frequency error < 0.1ppm<br><br>Freq. error < 1ppm; Amplitude > 90 % |
| Duty Cycle                 |                      | 45  | 50    | 55  | %           |   |
| Crystal C load             | C <sub>L</sub>       | 7   | 7.5   |     | pF          |   |
| Crystal tuning sensitivity |                      | 27  | 32    |     | ppm/pF      |   |
| Static range               | SR                   |     | ±50   |     | ppm         |   |
| Dynamic range              | DR                   |     | ±30   |     | ppm         |   |
| AFC tuning step            | F <sub>res-AFC</sub> |     | 0.007 |     | ppm/<br>DAC |   |
| AFC settling time          | T <sub>AFC</sub>     |     | 150   | 200 | μs          |   |
| Negative resistance        | -R                   | 100 |       |     | Ω           |   |
| Start-up time              |                      |     | 1     | 3   | ms          |   |
| Pushing figure             |                      |     |       | 1   | ppm/V       |   |

**SERIAL PORT**

Table 17

| Parameter  | Symbol | Min          | Typ | Max          | Unit | Test Conditions / Comments   |
|--|--------|--------------|-----|--------------|------|--|
| <b>DC Electrical Parameters (for DATA1/DATA2, CLK, and EN)</b> |        |              |     |              |      |  |
| Input High Voltage (V <sub>IH</sub> )                          |        | 0.8*<br>VINT |     |              | V    | All inputs (DATA1/DATA2, CLK and EN) use a Schmitt trigger input stage with a Pull Down<br>AC/DC |
| Input Low Voltage (V <sub>IL</sub> )                           |        |              |     | 0.2*<br>VINT | V    | AC/DC  |
| Input Current  |        | 5            |     | 30           | μA   | 0.2*VINT ≤ Vin ≤ VINT  |
| Input Capacitance  |        |              |     | 5            | pF   |  |
| <b>Timing Parameters</b>                                       |        |              |     |              |      |  |
| Write Operation  |        |              |     |              | ns   |  |
| T <sub>CLK</sub>   |        | 16.28        |     |              | ns   | Clock Period (1/61.44 MHz)   |
| T1   |        | 16.28        |     |              | ns   | Enable High to CLK High  |
| Ts   |        | 5            |     |              | ns   | Data Setup time  |
| Th   |        | 1            |     |              | ns   | Data Hold time   |
| T2   |        | 8.14         |     |              | ns   | CLK Low to Enable Low  |
| Tguard   |        | 16.28        |     |              | ns   | Enable Low to Enable High  |
| Read Operation   |        |              |     |              |      |  |
| T1   |        | 16.28        |     |              | ns   | Read request clock (1/61.44 MHz)   |
| T2   |        | 8.14         |     |              | ns   | CLK Low to Enable Low  |
| T4   |        | 16.28        |     |              | ns   | CLK Low to CLK High (Write to Read)  |
| T3   |        | 48.82        |     |              | ns   | Read Clock Period (3/61.44 MHz)  |
| T5   |        | 0            |     |              | ns   | CLK High to RX Output enable   |
| T6   |        |              |     | 16.28        | ns   | CLK Low to Output Disable  |

| Parameter                        | Symbol | Min   | Typ | Max | Unit | Test Conditions / Comments   |
|----------------------------------|--------|-------|-----|-----|------|--|
| <b>GMSK Data Write Operation</b> |        |       |     |     |      |  |
| Tgmskclk                         |        | 16.28 |     |     | Ns   | CLK Period (1/61.44 MHz)<br>Native Data rate in 2G filter is 4.33 MHz, 14 bit words. |
| T1                               |        | 16.28 |     |     | ns   | Enable High to CLK High  |
| T2                               |        | 8.14  |     |     | ns   | CLK Low to EN Low  |
| Tguard                           |        | 16.28 |     |     | ns   | Enable Low to Enable High  |

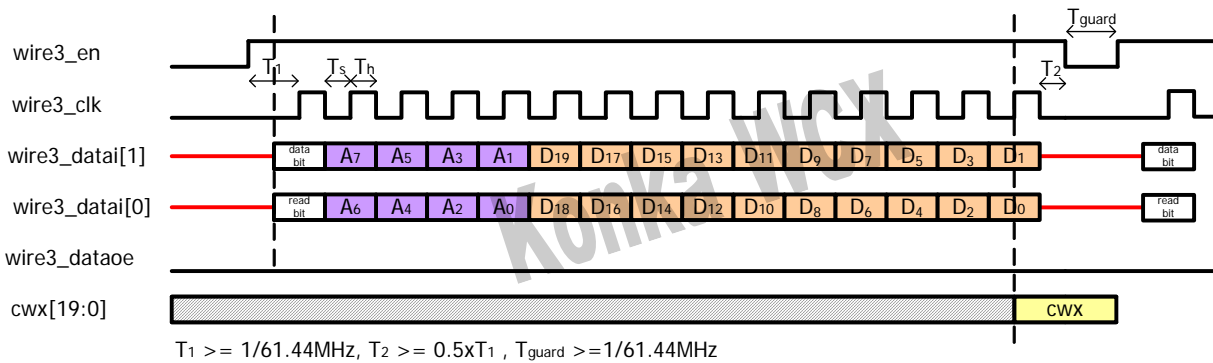


Figure 3: Serial Port Write Operation

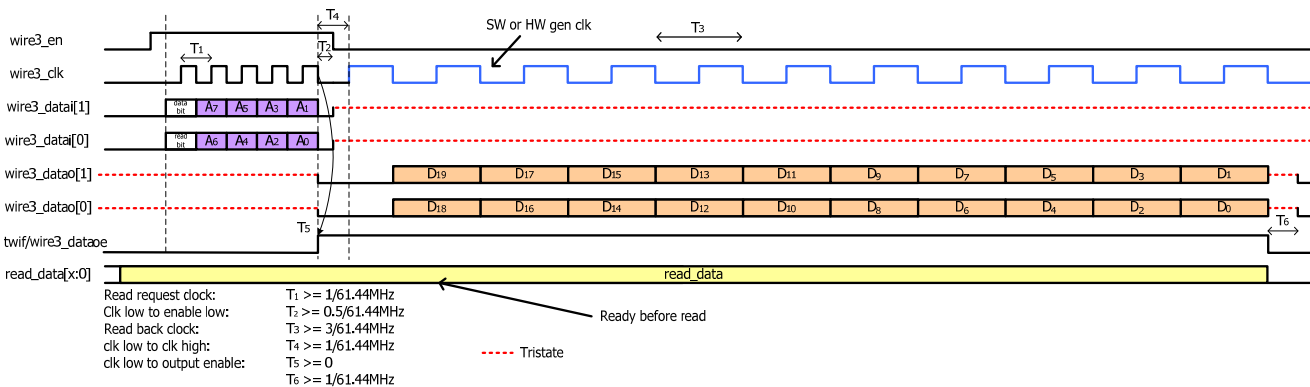


Figure 4: Serial Port Read Operation

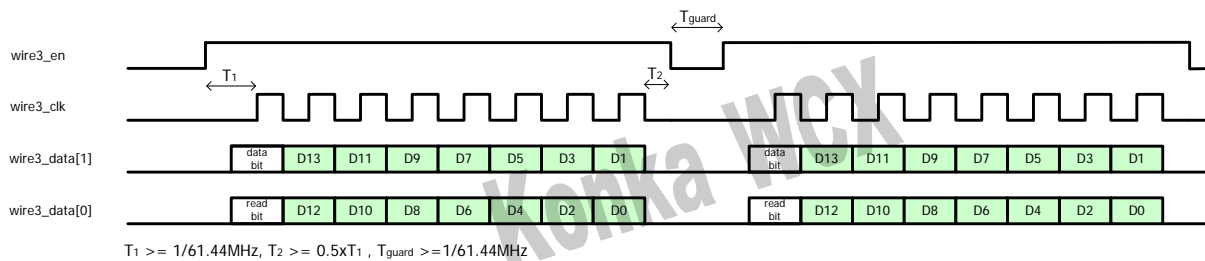


Figure 5. Tx Data Operation

**TYPICAL PERFORMANCE CHARACTERISTICS**

*Konka WCX*

**TBD**

*Konka WCX*

**THEORY OF OPERATION**  
**RECEIVER DESCRIPTION**

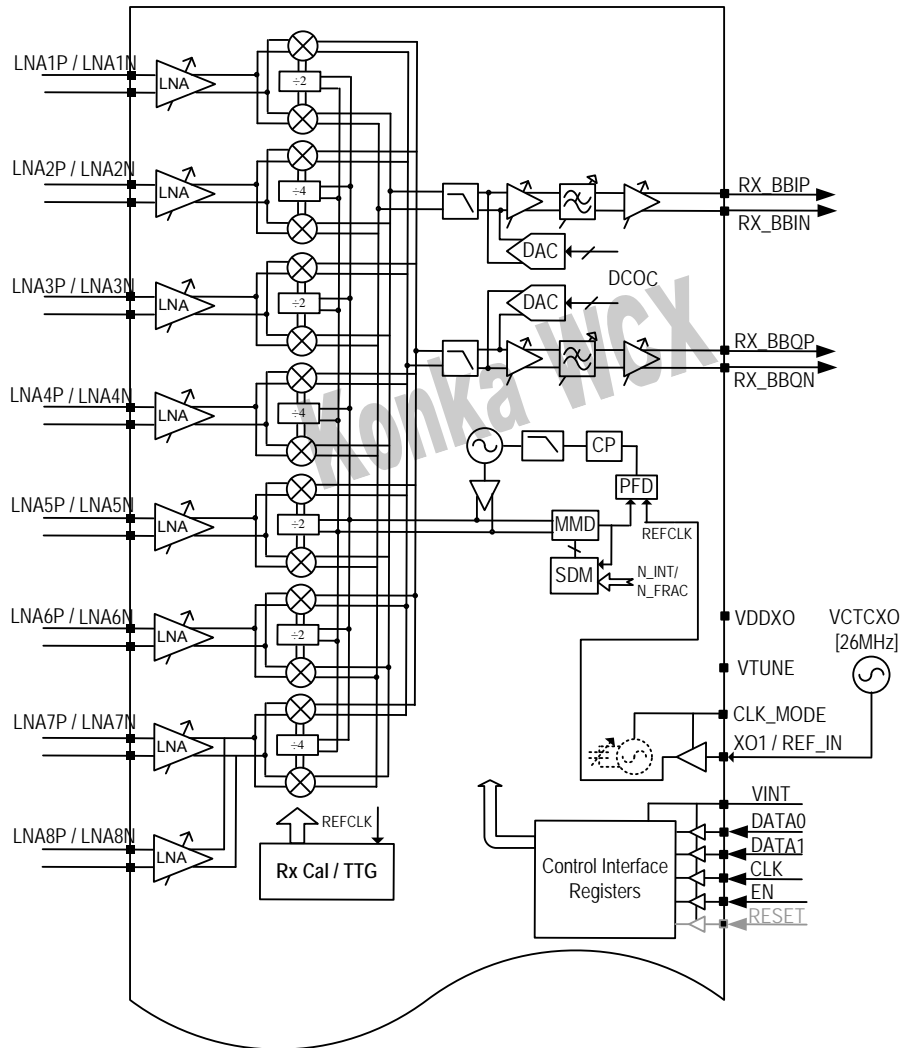


Figure 6: Block Diagram of Receiver Signal chain

The MT6162 direct conversion SAW-less receiver, designed to support 3GPP and GGE modes, includes the following functional blocks for each frequency band:

- Differential RF low noise amplifier (LNA)
- Differential I/Q demodulator
- Integrated frequency synthesizer with integrated VCO, LO buffers, and frequency divider-by-2
- Analog baseband channel select filter with automatic 3-dB corner frequency calibration mechanism
- Programmable gain amplifier with 3dB gain step
- DAC for DC offset cancellation
- Output drivers

- Image suppression calibration circuitry, which is activated at device initialization and supported by calibration routine in digital baseband

**LNAs**

There are eight differential LNA inputs in the receiver front-end specifically designed to be mode and frequency independent; the on-chip low-noise amplifiers require minimal external input matching network; each LNA comes with three gain steps (HI /MED/LO) to accommodate a larger receiver dynamic range, especially in Adjacent Channel Selectivity test case II as specified in 3GPP release 5,6, &7. The LNA settings are done through register LNA\_GAIN[1:0]. The I/Q demodulator has a

differential topology to minimize LO leakage and second-order IM distortion products referred to receiver's input.

### **Mixers**

High linearity quadrature mixer circuits are used to convert the RF signal to baseband in-phase and quadrature components. Two mixer sections exist, one optimized for the High band LNA outputs and one optimized for the Low band. The high band and low band mixer outputs are combined and then drive directly the first stage of the baseband low pass filter, which provides rejection for the largest blocking signals, prior to baseband amplification. Quadrature LO drive is provided to the mixers from the receiver synthesizer section via a DIV/2 or DIV/4 programmable divider, so that the same VCO can be used for both high and low bands. Excellent 90° quadrature phase and amplitude match are achieved by careful design and layout of the mixers and LO feeding network.

### **Baseband section**

The Rx channel filter can be reconfigured based on the operation mode: GSM/EDGE or 3G WCDMA. Channel selectivity is done partially on-chip in the analog baseband low-pass filter and the rest in digital baseband with extra margin added on adjacent channel blocker rejection. A Phase equalizer of 2<sup>nd</sup> order all pass network is required in the digital baseband to minimize receiver EVM for optimum HSDPA operation. When the receiver is operating in HSDPA 64QAM mode, the filter can be reconfigured for a 10% wider BW to reduce further Rx channel filter impairments. An automatic 3-dB corner frequency calibration is performed whenever the receiver is initialized. Analog baseband gain programmability is done in 3dB gain steps with the settings in the BB\_GAIN [3:0] register and according to BB gain. Calibration of DC offsets in the receiver is done at receiver initialization with an offset DAC connected at I/Q demodulator outputs to minimize differential DC offsets at receiver outputs for all RX gain steps.

### **DC Offset compensation**

Compensating for DC offsets is an inherent part of any Direct Conversion receiver solution. DC offsets can be characterized as falling into two categories:

- 1) Static or slow varying
- 2) Time varying

The MT6162 architecture has been designed to reduce the amount of time varying DC offsets. At receiver power-up, static DC offsets at receiver I/Q outputs are sampled at the Rx I/Q ADC converters. In the baseband section, a digital signal processing block is used to estimate the static DC offsets at different Rx baseband gain steps and store in LUTs found in register settings GMSKOFFS\_Q/\_I[8:0] and WCDMAOFFS\_Q/\_I[8:0]. During normal Rx operation, DC-offset DACs at mixer outputs are used to introduce the error term back into the receive signal path based on the assigned gain setting.

### **Image Rejection Calibration and Test Tone Generator (TTG)**

In conjunction with algorithms implemented in the baseband processor, the receiver can be calibrated for both quadrature phase and amplitude imbalance. This is important for higher order modulation systems to minimize impairments arising from the receiver. A test tone generator is used to produce a RF carrier that is then mixed down through the receiver produces a quadrature baseband tone. These tones are used by the baseband to calculate the quadrature error so that a correction can be applied. All corrections are applied in the digital domain within the baseband processor.

The intended operation is to apply the calibration when a new link is brought up i.e. at each specific RF channel frequency. Since reception is potentially continuous (for WCDMA/HSPA) then the accuracy of the corrections need to be maintained over temperature and gain setting without the need to re-calibrate.

The calibration is performed with the LNA off (and the external band select switch "open") to minimize the effects of any large interfering signals at the antenna and to avoid any leakage from the test tone to antenna causing spurious conducted emissions.

TRANSMITTER DESCRIPTION

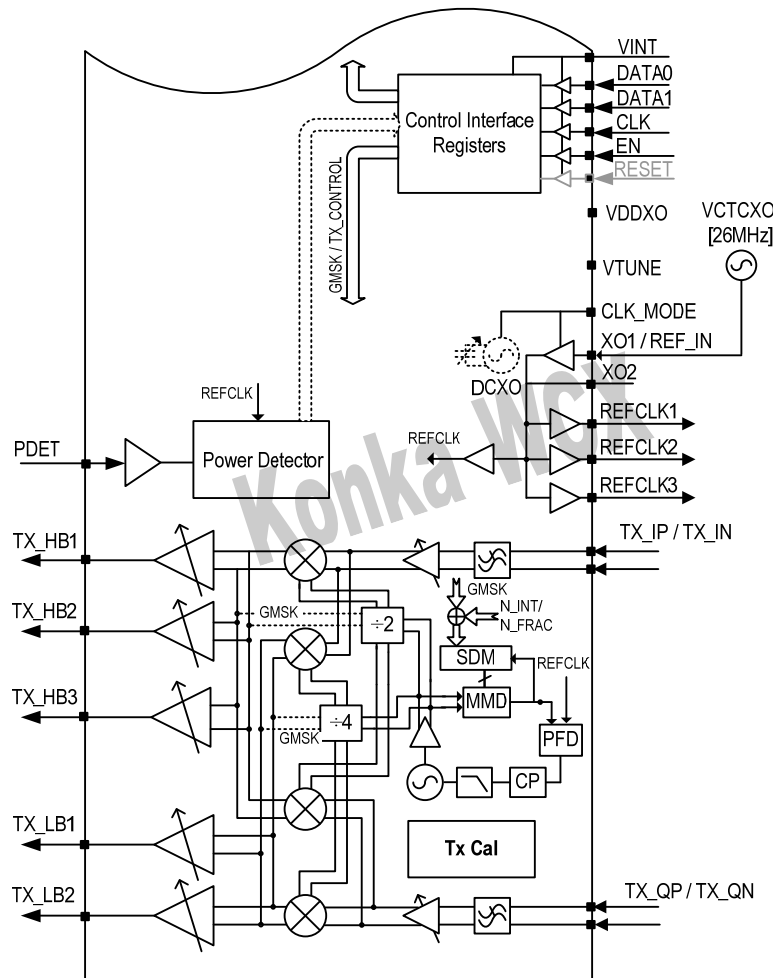


Figure 7: Block Diagram of Transmitter Signal chain

The MT6162 direct conversion SAW-less transmitter, designed to support 3GPP and EDGE modes, include the following functional blocks for each frequency band:

- 2<sup>nd</sup> order baseband low-pass filter
- Baseband programmable gain amplifier (PGA)
- Differential I/Q modulator
- Integrated frequency synthesizer with integrated VCO, LO buffers, and frequency divider-by-2/-4
- RF power amplifier driver with programmable variable gain and with single ended outputs
- LO feed-through and sideband suppression calibration circuitry, which is activated at device initialization and supported by calibration routines in digital baseband
- RMS power detector circuit, for use in the feedback path for closed-loop TX Power Control

In the GMSK mode, the high-resolution sigma-delta modulator in the synthesizer allows the direct digital

modulation at RF of the synthesizer and VCO Tx blocks. GMSK data is fed over the serial bus; Gaussian pulse shaping and loop-filter compensation are implemented as digital blocks in the digital baseband section.

**I/Q Baseband**

The baseband interface for the I and Q channels is a differential, DC coupled input, supporting a common mode voltage ( $V_{CM}$ ) centered at  $1.1 \pm 0.05V$ . The maximum supported single-ended signal amplitude is 500 mV peak to peak, which corresponds to 1.0V peak-peak differential on the I and Q channels.

Prior to the Quadrature Modulator, the I and Q channels each pass through a second order filter with a nominal cutoff frequency of ~6.0 MHz. The filter provides the required rejection for DAC images and noise emissions from digital Baseband IC. The filter also helps to reject any spurious signals that can be coupled to the baseband terminals on the PCB.



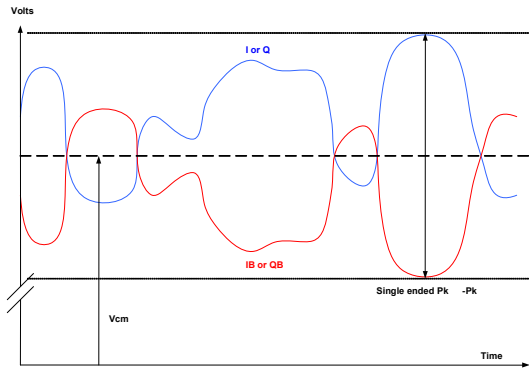


Figure 8: TX I/Q Modulator input levels

**Special Considerations: (i) HSUPA Mode, (ii) MMMB operation mode**

(i) In typical WCDMA TX mode, constant I/Q input signal RMS voltage is used for all TX output power levels. In HSUPA TX modes (with HS-DPCCH only or with E-DCH), the digital baseband IC is required to reduce the input signal I/Q RMS voltage accordingly, based on the Maximum Power Reduction (MPR) as specified in 3GPP standard. As a result, no additional Tx BB gain adjustment is required. (ii) Two TX outputs (1LB, 1HB) are dedicated for GGE mode only, and they are designed to drive GGE mode only quad-band PAs. For the case in which the power amplifier can operate in both GGE and 3G modes and over different bands, the 3G mode TX outputs are used to drive the Multi-Mode Multi-Band PA (refer to Table7). In GGE mode, the TX output power is variable and can be set to a level higher than that of GGE mode only outputs.

**TX LO Feed-Thru and Sideband Suppression Calibrations**

Upon powering up, TX carrier leakage or LOFT and sideband suppression calibrations are performed automatically for each band's center frequency channel. In

MT6162, the carrier leakage calibration is performed before the sideband suppression calibration. The carrier leakage calibration requires both RX and TX frequency synthesizers to be ON. The digital baseband IC is required to output a constant DC signal during this calibration process. For sideband suppression calibration, the digital baseband IC is required to deliver CW tones at Tx BB I/Q inputs. During both carrier and sideband suppression calibrations, the transmitter gain is varied in order to perform the calibration at different output power levels.

**RMS Power Detector**

The MT6162 power detector is a direct conversion receiver optimized for very stable gain to allow accurate power measurements. The power detector absolute accuracy is calibrated with a single calibration at ambient temperature in each 3GPP band. It contains I/Q mixers and uses the TX synthesizer to downconvert the feedback signal to baseband; the signal is filtered and sampled by detector ADC (Figure 2.1). To allow fast measurements without data dependency an additional reference signal path is provided. The ADC is shared between this reference path and the main power detector path. The system is designed to work with a coupler and attenuator so that the PA output power can be sensed. The RMS voltage is digitally estimated both at the baseband inputs and at the RF feedback pin, so that the gain of the Tx chain including PA, etc. can be calibrated within microseconds, regardless of short-term statistical variations in the AM envelope of the baseband signals. This technique ensures the RMS power is accurately measured independent of type of modulation or traffic channel configuration. The power detector features fast settling time, typically 5us, and can be powered down during the majority of the time, adding little current consumption to the total solution.

For LO feed-through and sideband suppression calibration purposes, the detector measurement path can be re-used together with a separate feedback LNA to measure the output of the Tx drivers. In this case, the internal ADC is no used and instead the calibration signal is connected to the receiver baseband output pins.

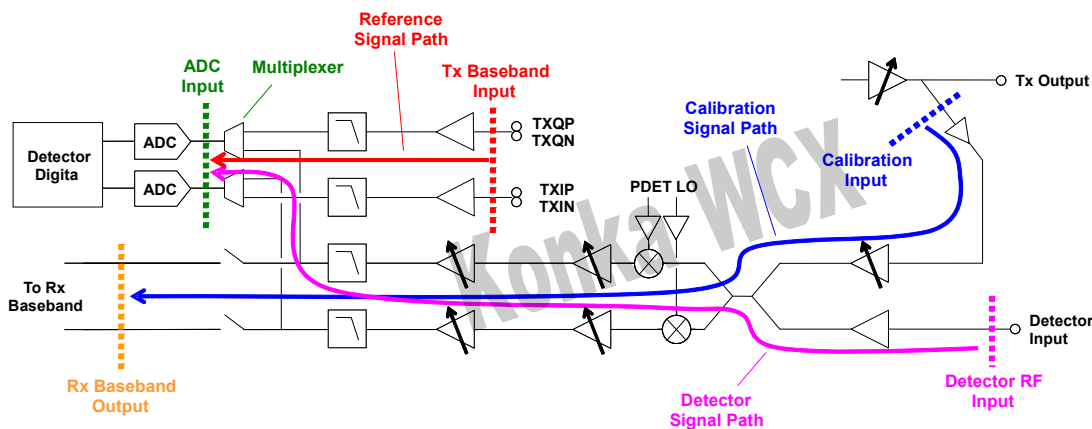


Figure 9: Power Detector Interface and Signal Path Definition

**POWER MANAGEMENT**

For optimum power efficiency the MT6162 operates from several external supplies some of which are intended to be supplied by linear regulation of the system supply/battery and some via a switched mode power supply. On chip regulation ensures that noise and switching transients on these supplies are rejected so a well conditioned internal supply network is available. The required supplies to the IC are specified in Table 18.

The internal supplies VSUP1-VSUP3 are those connected to external pins and require a decoupling capacitor to achieve the required noise and AC power supply rejection. These LDO's are described in more detail in Table 19 with the recommended component values.

**FREQUENCY SYNTHESIS**

The MT6162 contains two independent frequency synthesizers; one for Transmit and one for Receive. The principle of operation for both systems is essentially the same, although the respective VCOs are tuned for the appropriate TX or RX frequency bands. In GMSK Tx mode, the frequency synthesizer is operated in Direct-Frequency Modulation mode (DFM), with data being to the DFM engine over the serial port interface. The block diagram for Rx synthesizer is shown in Figure 10.

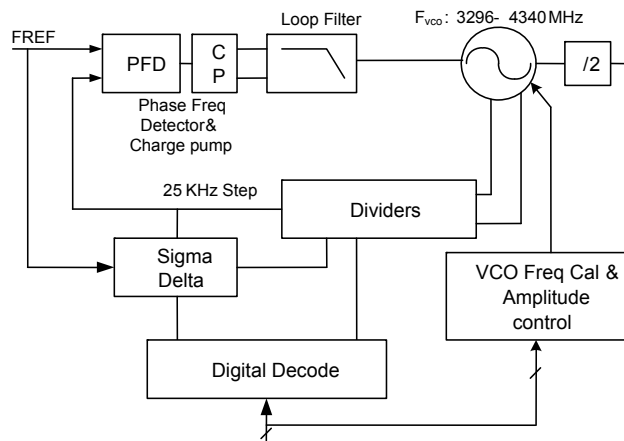


Figure 10: Frequency Synthesis Block Diagram (Receiver)

All the components are fully integrated for both TX and RX, including dividers, VCOs, respective tank components, and loop filters. The VCOs have a wide tuning range, necessary to cover all the major 3GPP bands. The VCOs run at 2x the high frequency band and 4x the low band frequency. This minimizes VCO leakage power at the wanted frequency, and tuning range requirements of the VCO. The design incorporates both frequency and amplitude calibration to ensure the oscillator is always operating with its optimum performance. The calibrations occur during the PLL lock

time and are fully self-contained requiring no user inputs. VCOs are configurable for both GGE & 3G requirements. The on-chip nature of all the components allow for optimum matching conditions, and minimal power consumption for the entire system. Careful layout and VCO shielding techniques are used to minimize any unwanted coupling effects. The dividers employ advanced design techniques to achieve very low power in operation translating to an extended standby time of the handset.

For a high performance loop, the MT6162 PLLs implement fractional-n architectures, with a high comparison frequency used in the Phase Frequency Detector (PFD). This gives the advantages of faster lock time and lower in-band noise floor. The fractional-N functionality is implemented with a 3<sup>rd</sup> order Sigma Delta modulator which is designed for low current operation. The Phase Frequency Detector (PFD), Charge pump and loop filter are internally trimmed to remove variations associated with process and frequency. This process is fully automated on-chip.

The Synthesizer programming fractional and integer words is via the standard serial interface with separate registers for TX & RX. The channel resolution is 3Hz and 25kHz for Tx and Rx synthesizers, respectively.

**Reference Path**

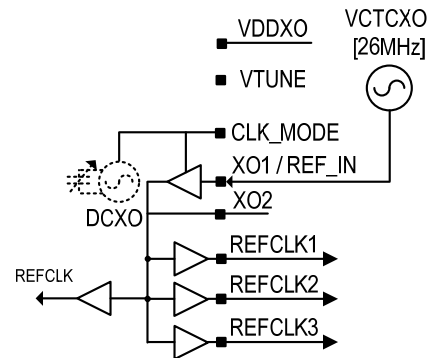


Figure 11: Reference Path

The MT6162 requires the standard frequency of 26 MHz as a reference input. Either this can be from an external VCTCXO, or on-chip DCXO circuit with AFC tuning and external crystal oscillator. The 26 MHz is internally buffered and distributed to the respective blocks, such as the synthesizer PFDs. The MT6162 provides three buffered outputs; one of them will go mainly to the digital baseband on-chip PLL system use to generate the clocks for Rx ADCs and Tx DACs. The additional buffers are available for driving auxiliary IC's such as connectivity solutions. The output buffers can be disabled via the serial interface.

| Supply    | Usage                          | Regulator Type | Voltage | Voltage Tolerance | Iave / Imax |
|-----------|--------------------------------|----------------|---------|-------------------|-------------|
| VINT      | Serial interface control logic | Switching      | 1.8V    | ±125mV            | 6mA/10mA    |
| VDDXO     | Regulated supply for VCXO/DCXO | Linear         | 2.8V    | ±100mV            | 3.5mA/5mA   |
| VDD_18    | Regulated Supply for IC        | Switching      | 1.825V  | ±75mV             | 100mA/140mA |
| VDD_28a/b | Regulated supply for IC        | Linear         | 2.85V   | ±100mV            | 53mA/85mA   |

VDD\_28a and VDD\_28b should be shorted together on the PCB (there is no internal connection)

Table 18 Power Supply Configuration

| Supply   | Usage   | Connection                                | Nom O/P Voltage |
|----------|---|---|-----------------|
| VSUP1    | Receiver Supply (low noise blocks)<br>Regulated from VDD_18     | External Decoupling Capacitor<br>Cnom=1µF | 1.65V           |
| VSUP2a/b | Transmitter Supply (low noise blocks).<br>Regulated from VDD_18 | External Decoupling Capacitor<br>Cnom=1µF | 1.65V           |
| VSUP3    | Transmit Supply Regulated from<br>VDD_28a/b                     | External Decoupling Capacitor<br>Cnom=1µF | 2.5V            |

VSUP2a and VSUP2b should be shorted together on the PCB (there is no internal connection)

Table 19 Internal Supplies Configuration

**SERIAL INTERFACE**

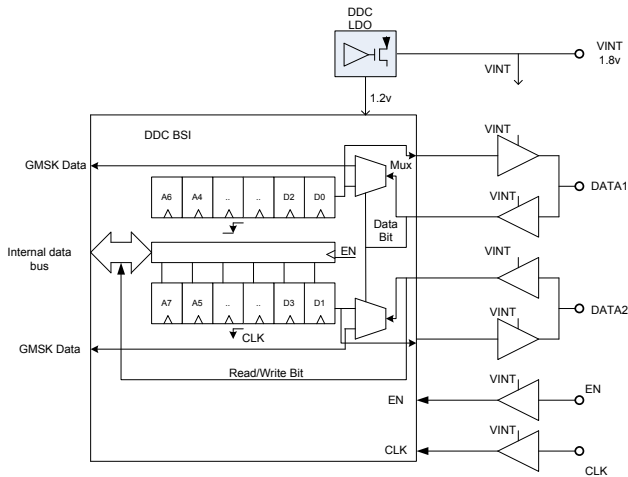


Figure 12. Serial Interface

The MT6162 uses a 4-wire bidirectional interface (BSI) for all communications with the baseband processor: writing control words, sending data to the DFM engine and reading back from the power detector. The serial interface contains four lines: Clock (CLK), two Bidirectional data (DATA1 & DATA2), and an active high chip select (EN) lines. The serial

interface supports both write and read access protocols. Hardware details are described in the data sheet.

The types of words supported are:

- a) Write (Control)
- b) Read including Read request
- c) DFM word (GMSK Data)

Serial port Write Control words are a fixed length of 30 bits over two data lines. The first 2 bits are mode selection for the BSI; The next 8 bits are address and the final 20 bits are data. DFM Data only contains 2 mode and 14 data bits; no address bits are required (Figure 5). DATA is sampled on the rising edge of CLK. The MSB of write and read words are transferred first; LSB last. The Read data is transferred out on the falling edge of the BSI clock.

The MT6162 Mode word formats are shown in Table 20:

| Data | Read | Type of word    |
|------|------|-----------------|
| 0    | 0    | BSI Write word  |
| 0    | 1    | BSI Read word   |
| 1    | 0    | DFM (GMSK Data) |

Table 20: Word Formats for MT6162 Serial Interface

APPLICATIONS

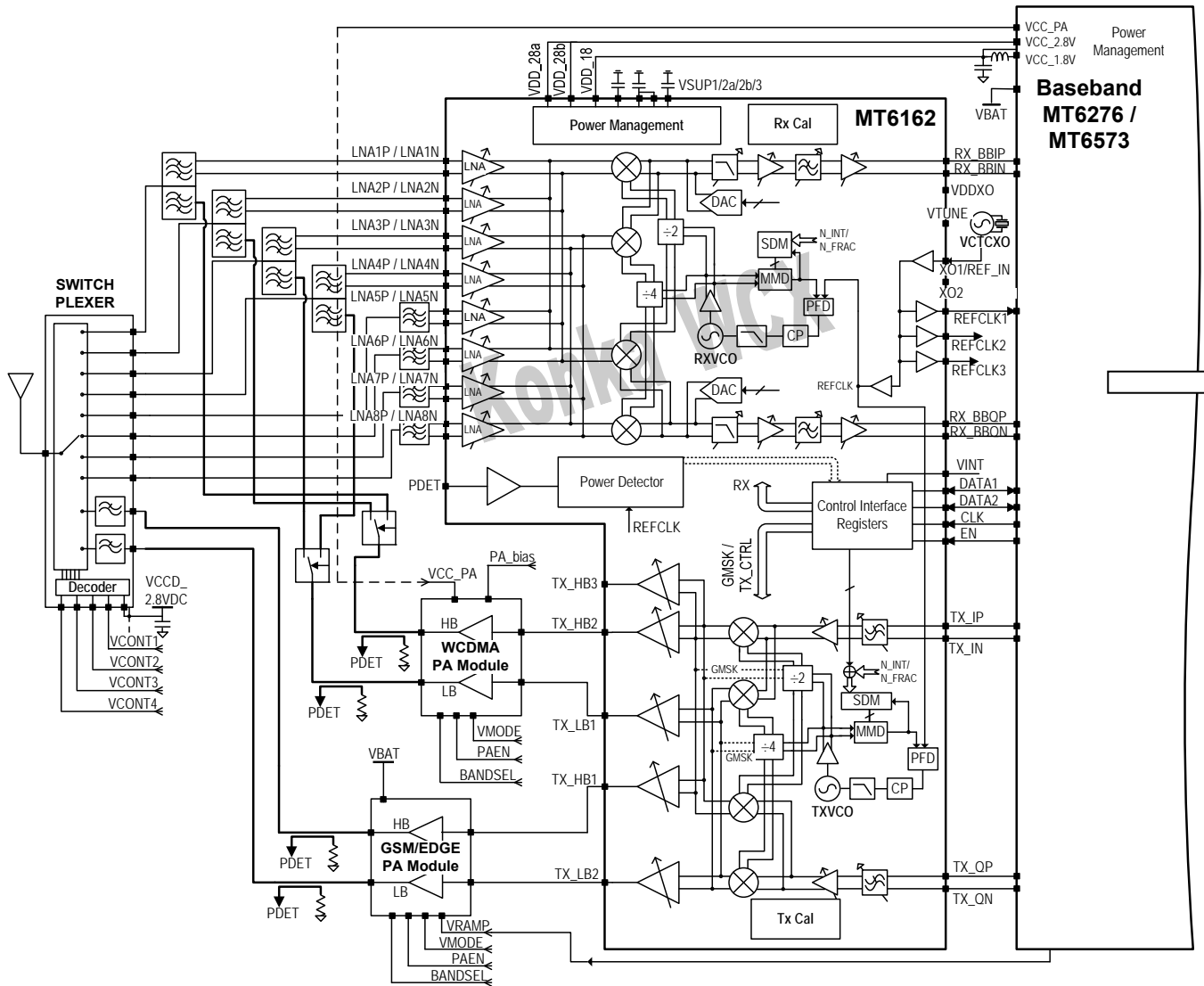


Figure 13: Multi-Band Multi-Mode Platform.

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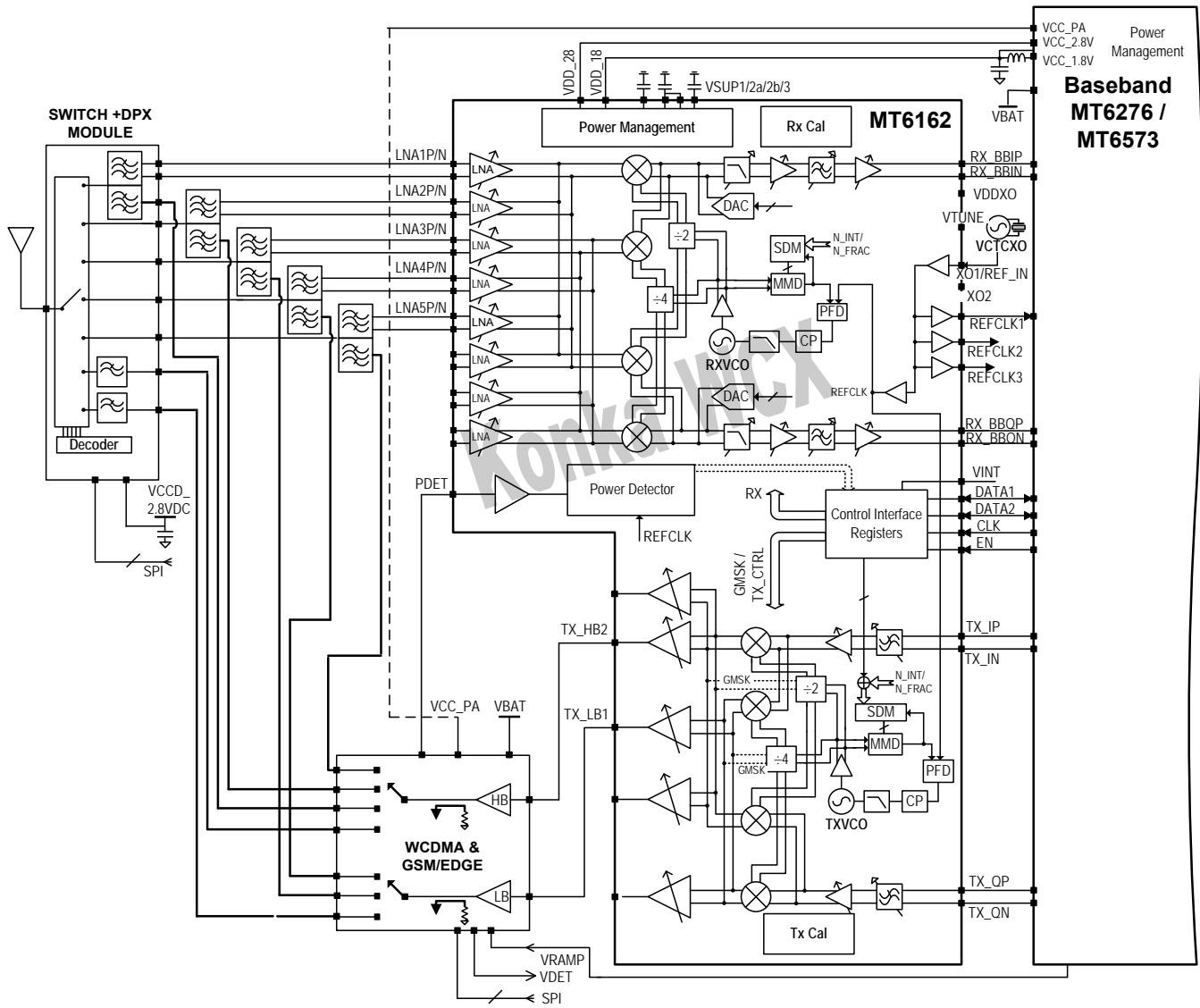


Figure 14: Multi-Band Multi-Mode platform, with MMMB PA configuration.

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OUTLINE DIMENSIONS

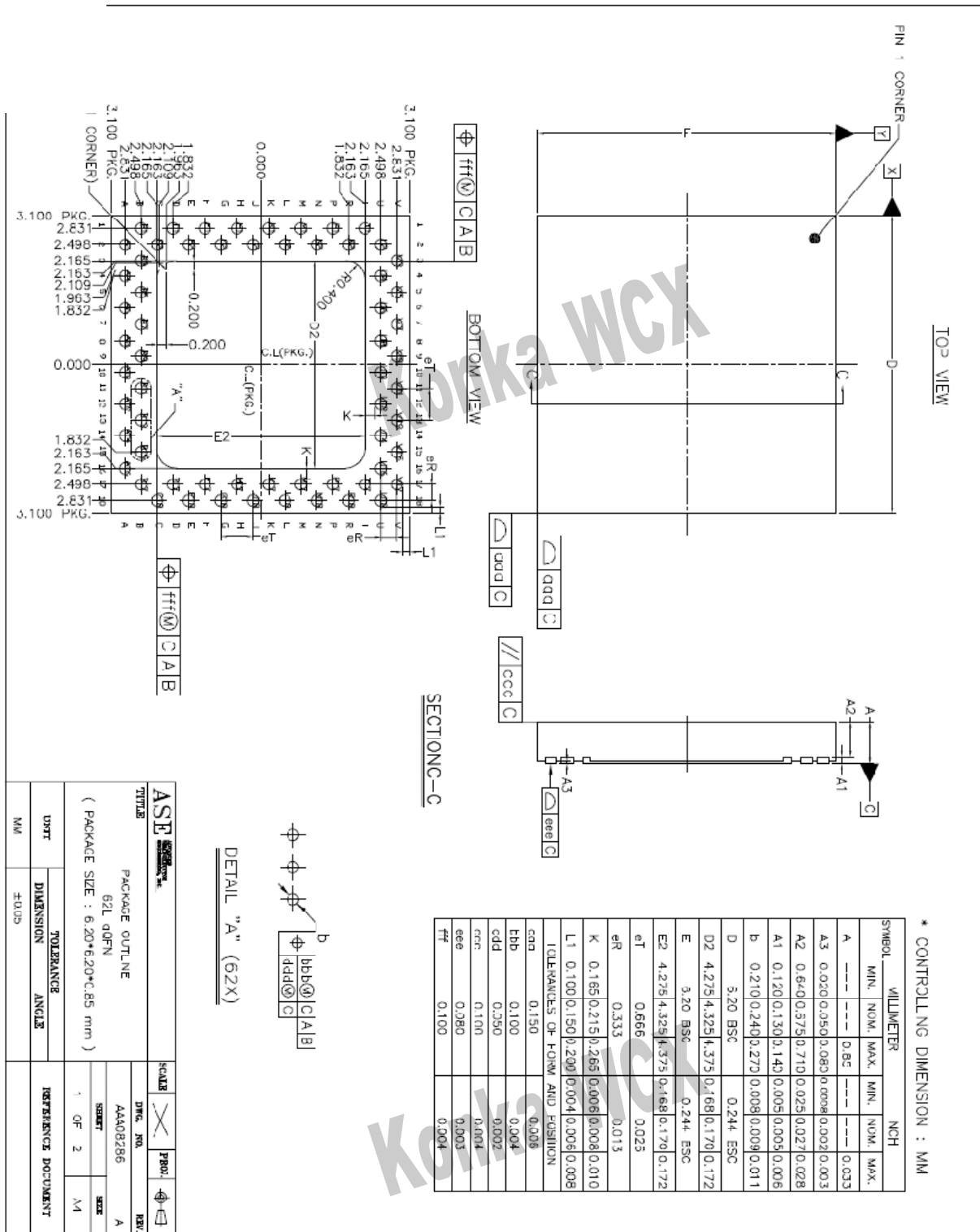


Figure 15.

**ORDERING GUIDE**

| <b>Model</b> | <b>Temperature Range</b> | <b>Package Description</b>     | <b>Package Option</b> |
|--------------|--------------------------|--------------------------------|-----------------------|
| MT6162       | -30 °C to +85 °C         | aQFN (6.2x6.2mm <sup>2</sup> ) | -L Lead Free          |

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**REVISION HISTORY**

| <b>Revision</b>  | <b>Date</b>                  | <b>Silicon</b> | <b>Description</b>   |
|------------------|------------------------------|----------------|--|
| <b>Pro – 1.0</b> | 12 <sup>th</sup> Oct 2009    | Rev 0.x        | Initial review Document.   |
| <b>Pro – 1.1</b> | June 02, 2010                |                | - Based on 'Othello_H_Test_List-Ver1.1.xls'<br>- Taking into account feedback from TM on v1.0 document |
| <b>Pro – 1.2</b> | Sept 30 <sup>th</sup> , 2010 |                | Sept. 30 <sup>th</sup> datasheet review  |
| <b>Pro – 1.3</b> | Feb 14 <sup>th</sup> , 2011  | ES2            | To be released to customers  |
| <b>Pro-1.4</b>   | Mar 17 <sup>th</sup> , 2011  | ES2            | Corrected POD (Package Outline drawing)  |
| <b>Pro-1.5</b>   | Mar 20 <sup>th</sup> , 2011  | ES2            | Removed unwanted references  |
|                  |                              |                |  |
|                  |                              |                |  |
|                  |                              |                |  |
|                  |                              |                |  |

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